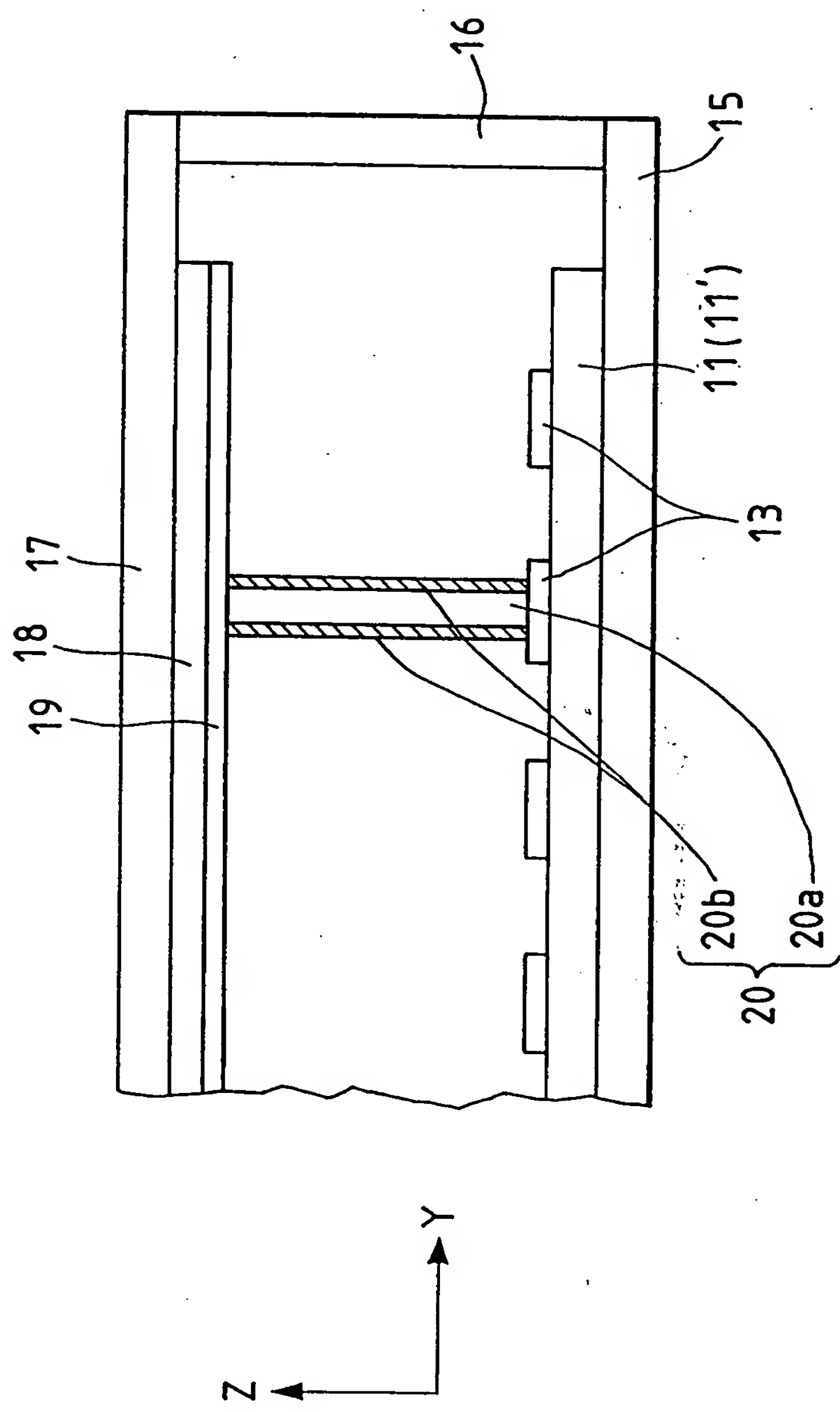


6274972

6274972

1/31

FIG. 1



63
FIG. 63

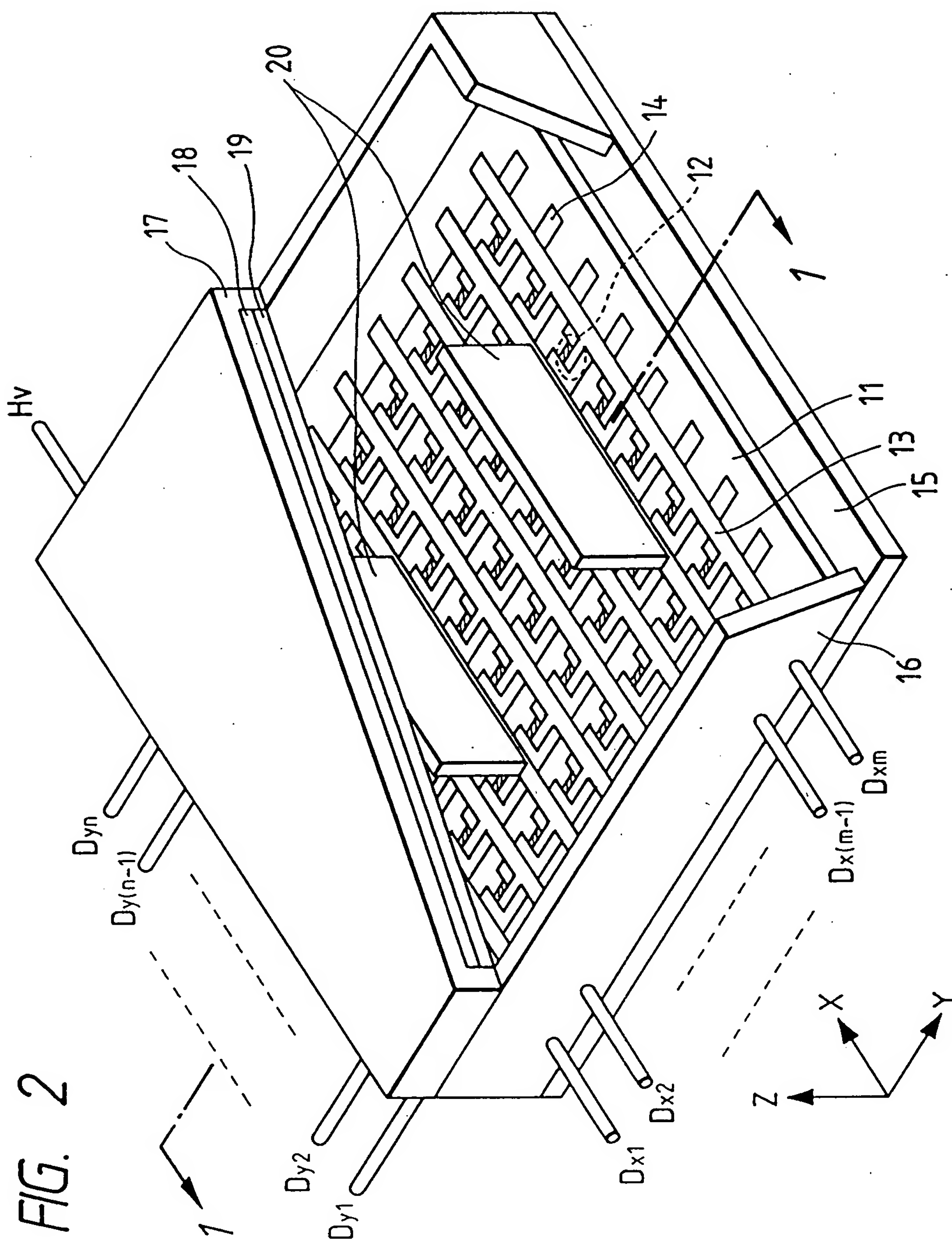
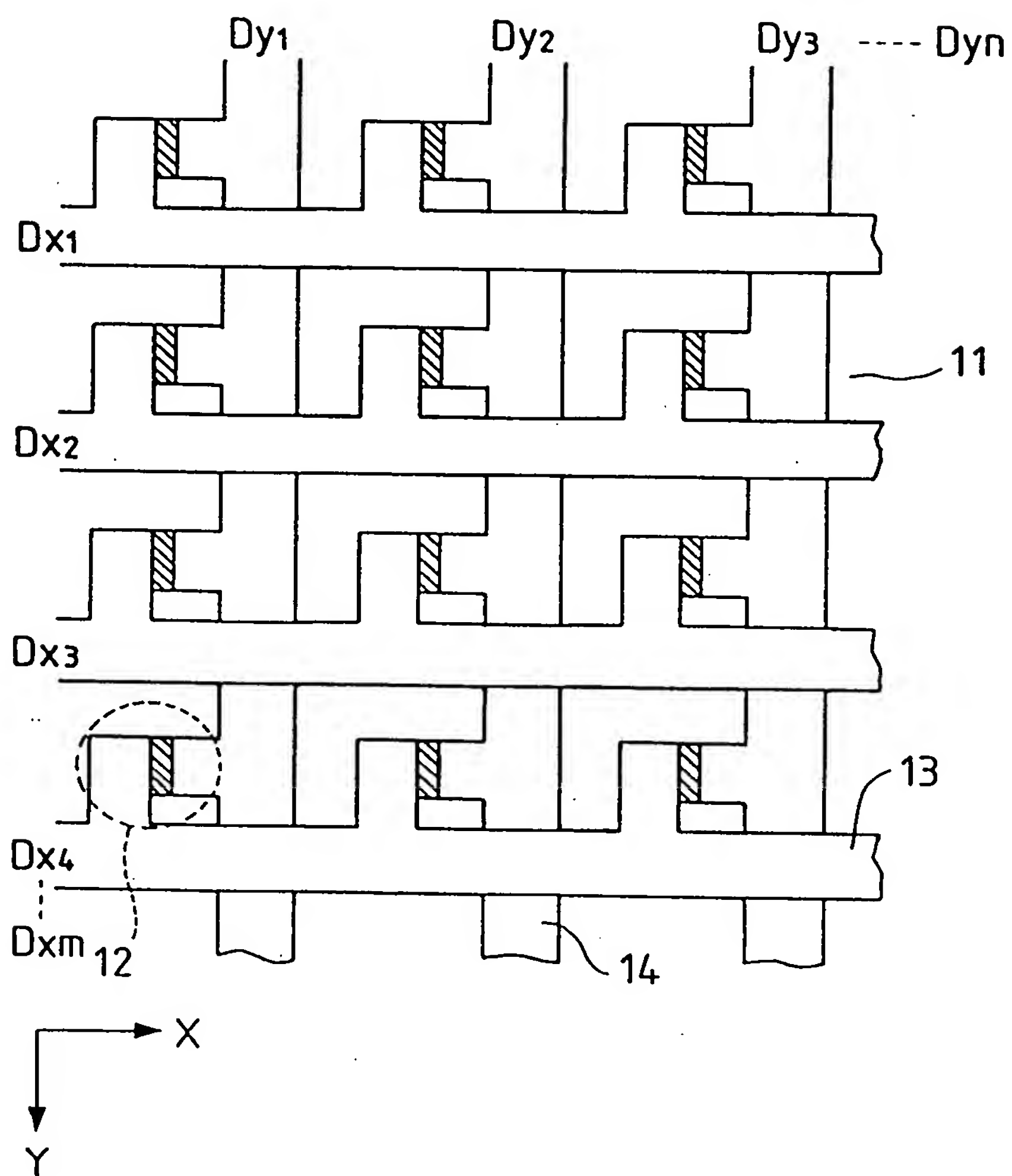


FIG. 3



86E2E0 T8954050

FIG. 4A

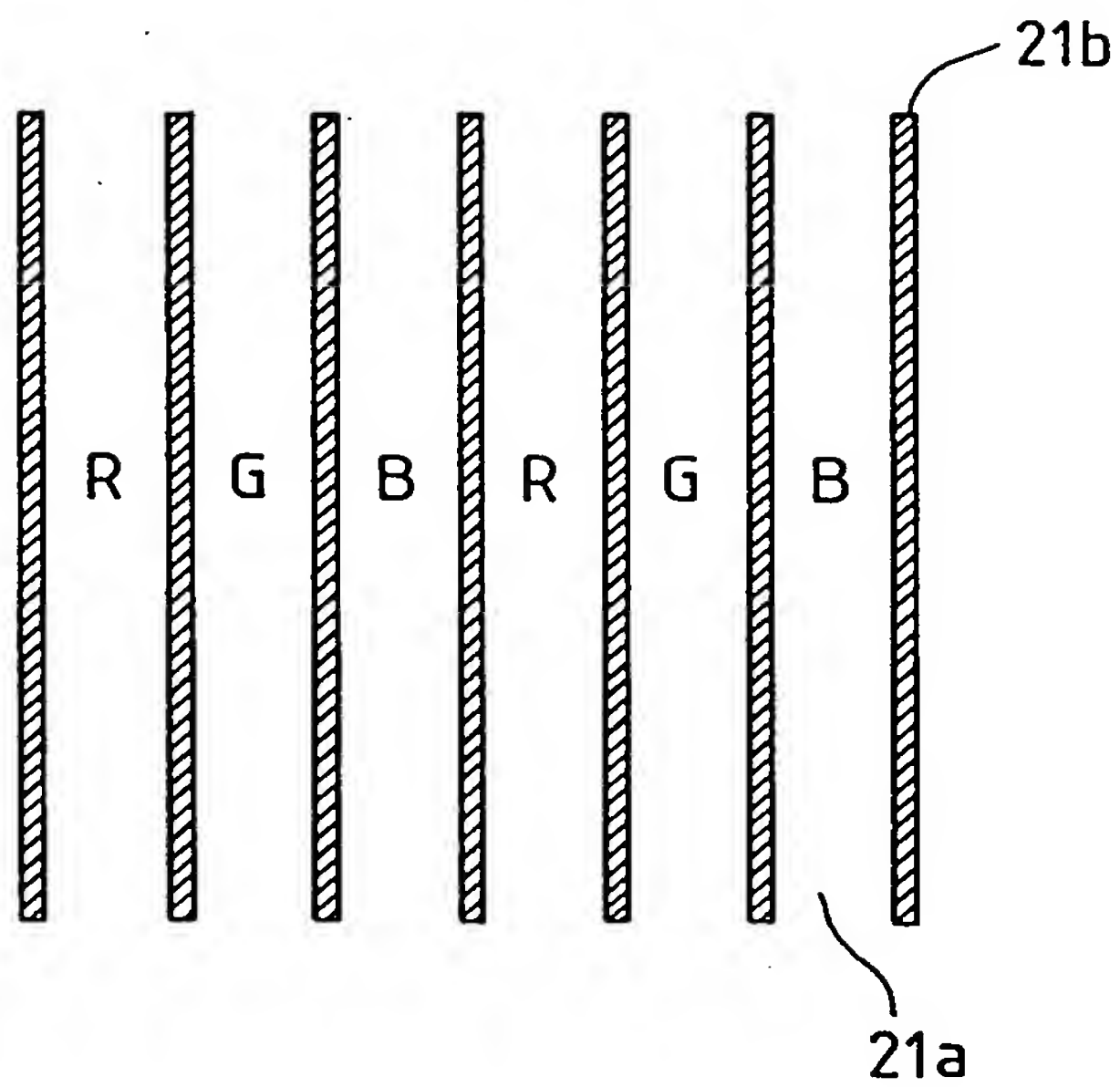


FIG. 4B

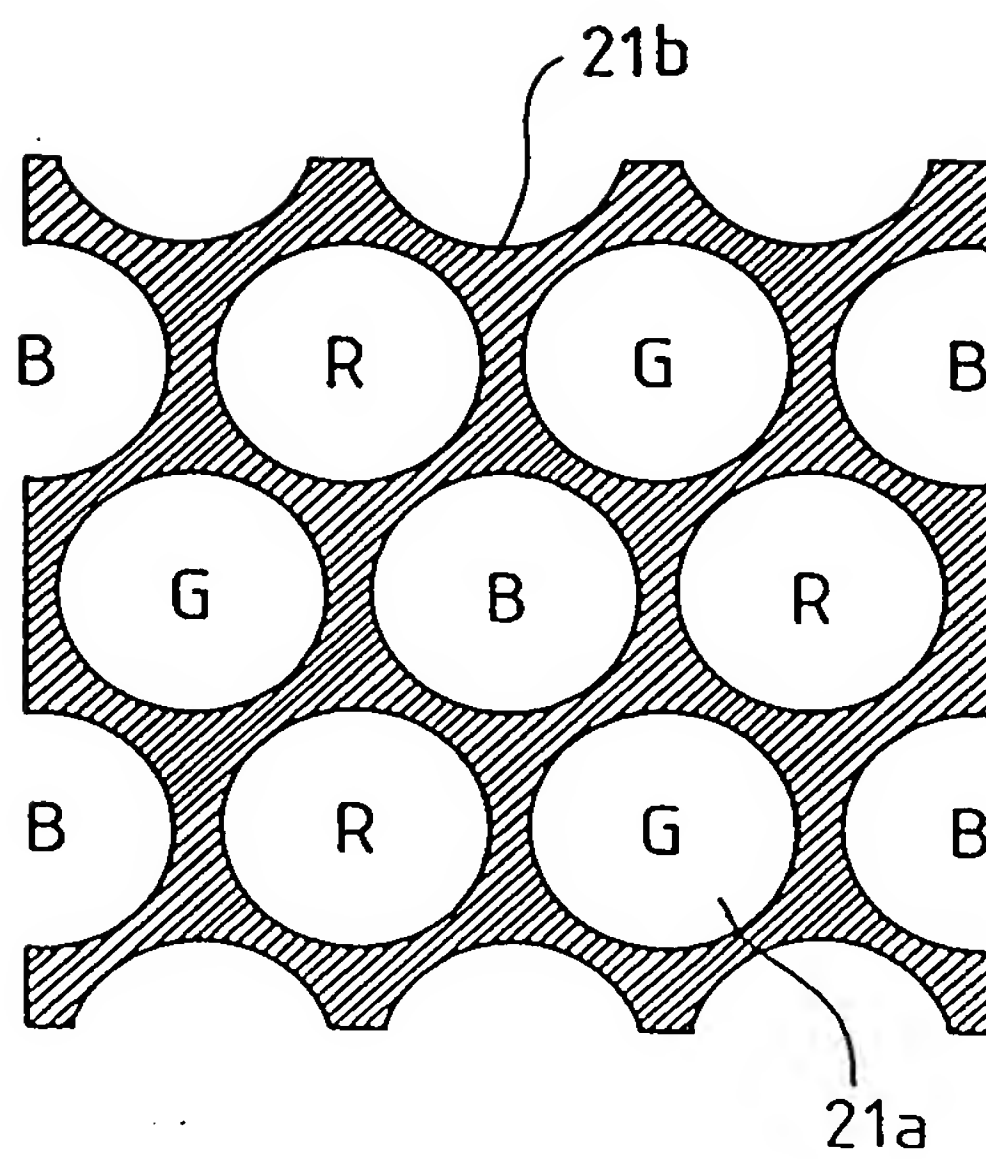
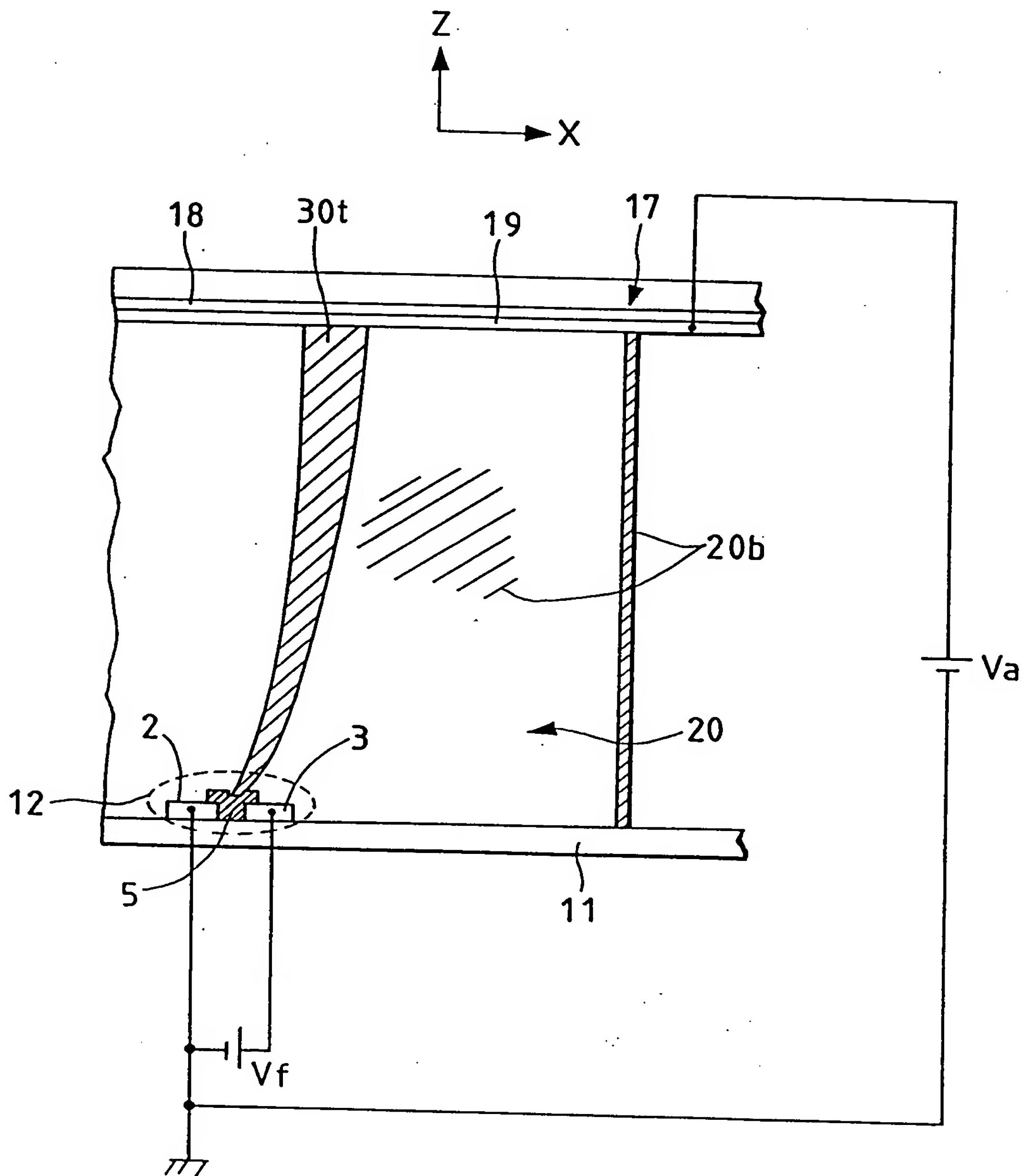


FIG. 5



A 3D coordinate system is shown with a vertical axis labeled 'Z' and a horizontal axis labeled 'Y'.

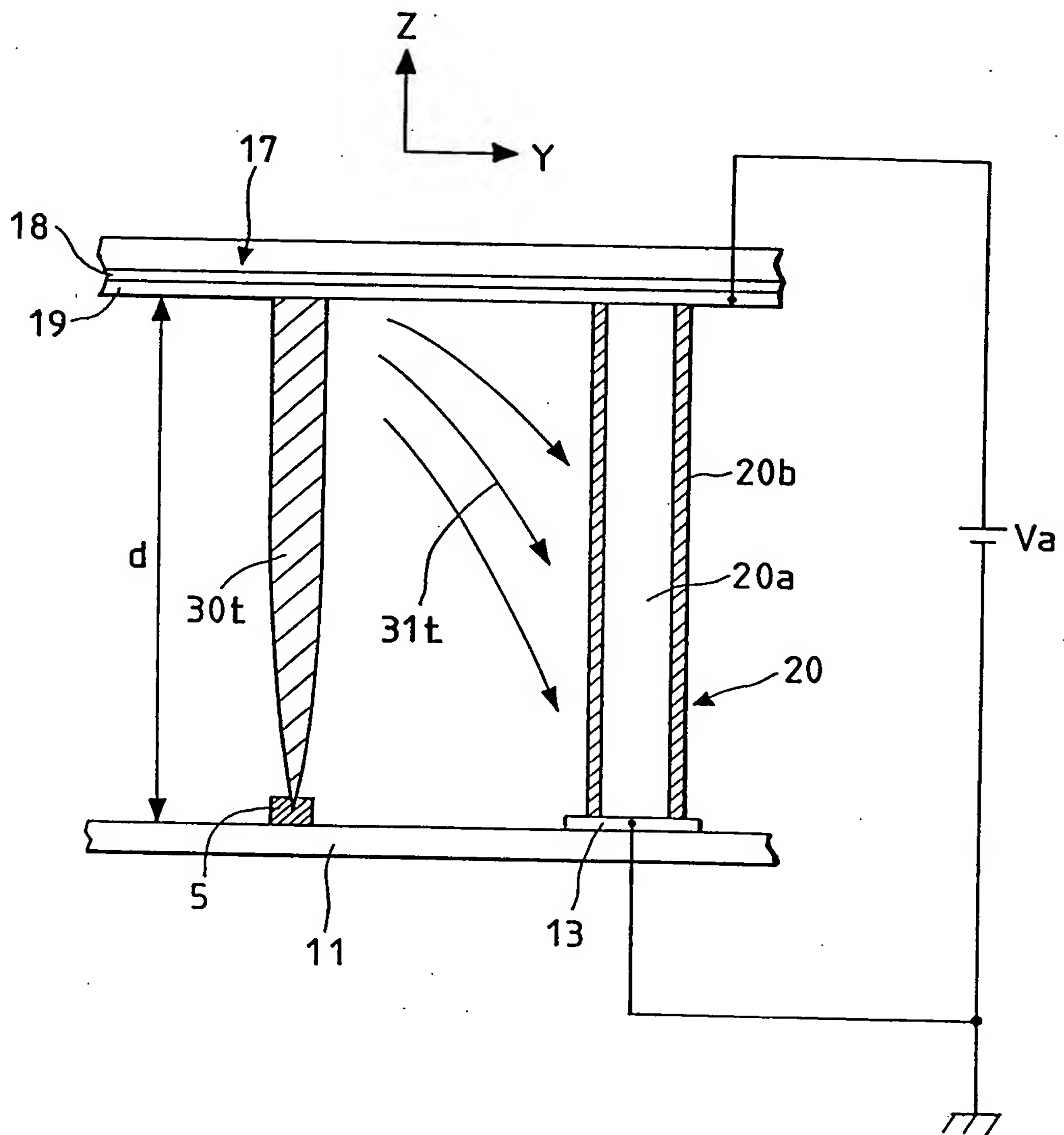


FIG. 7A

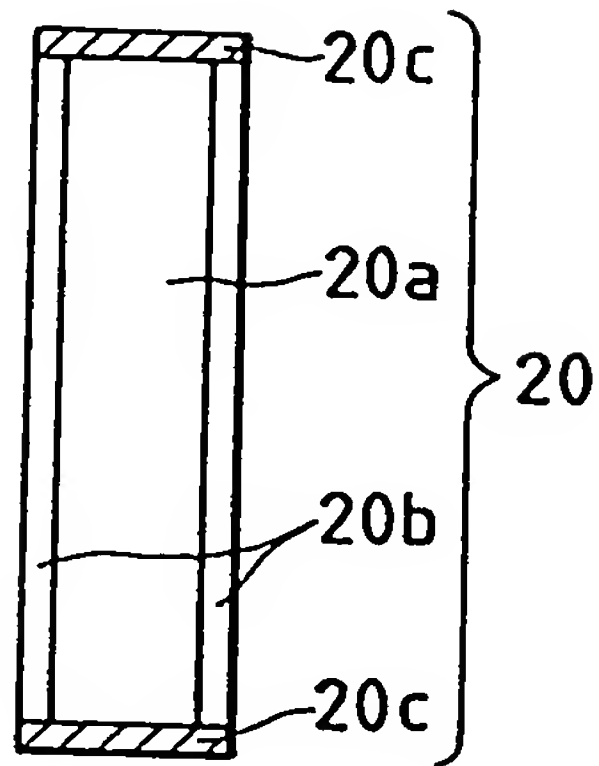


FIG. 7B

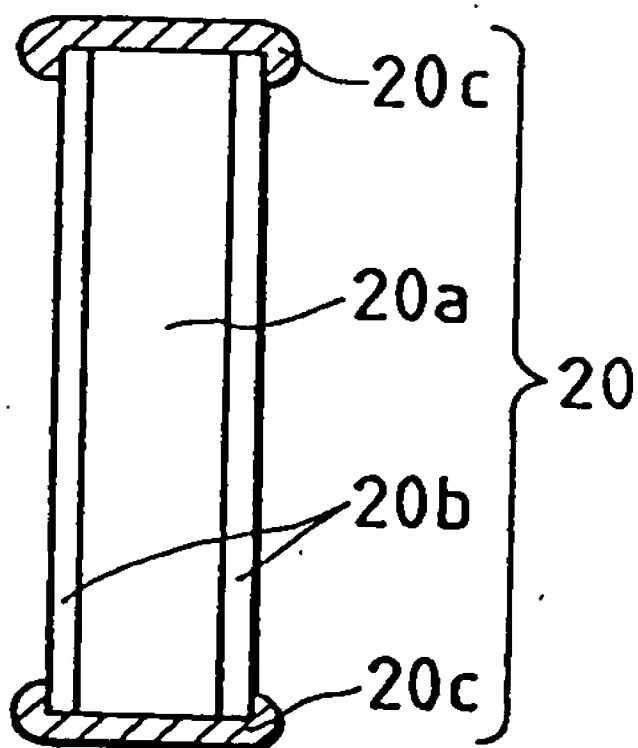


FIG. 7C

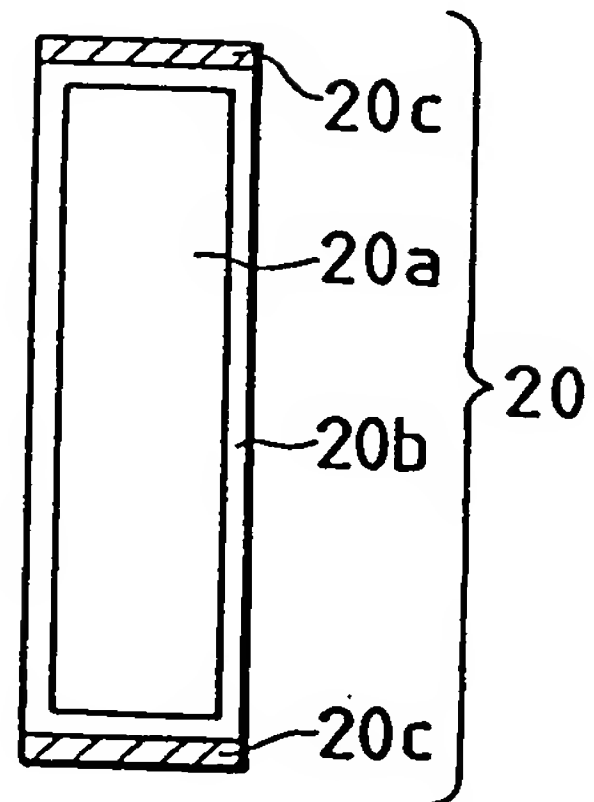


FIG. 8

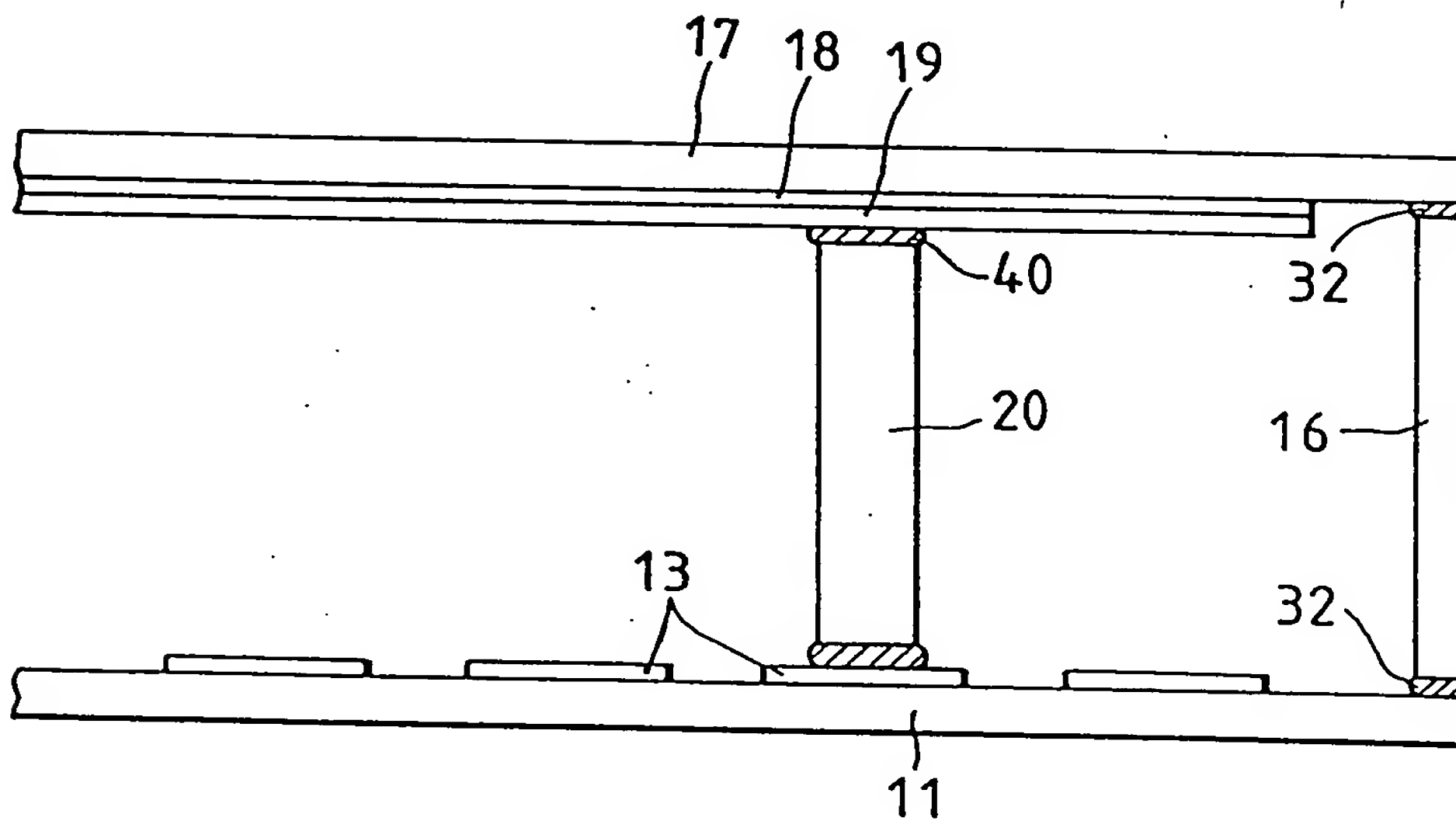


FIG. 9A

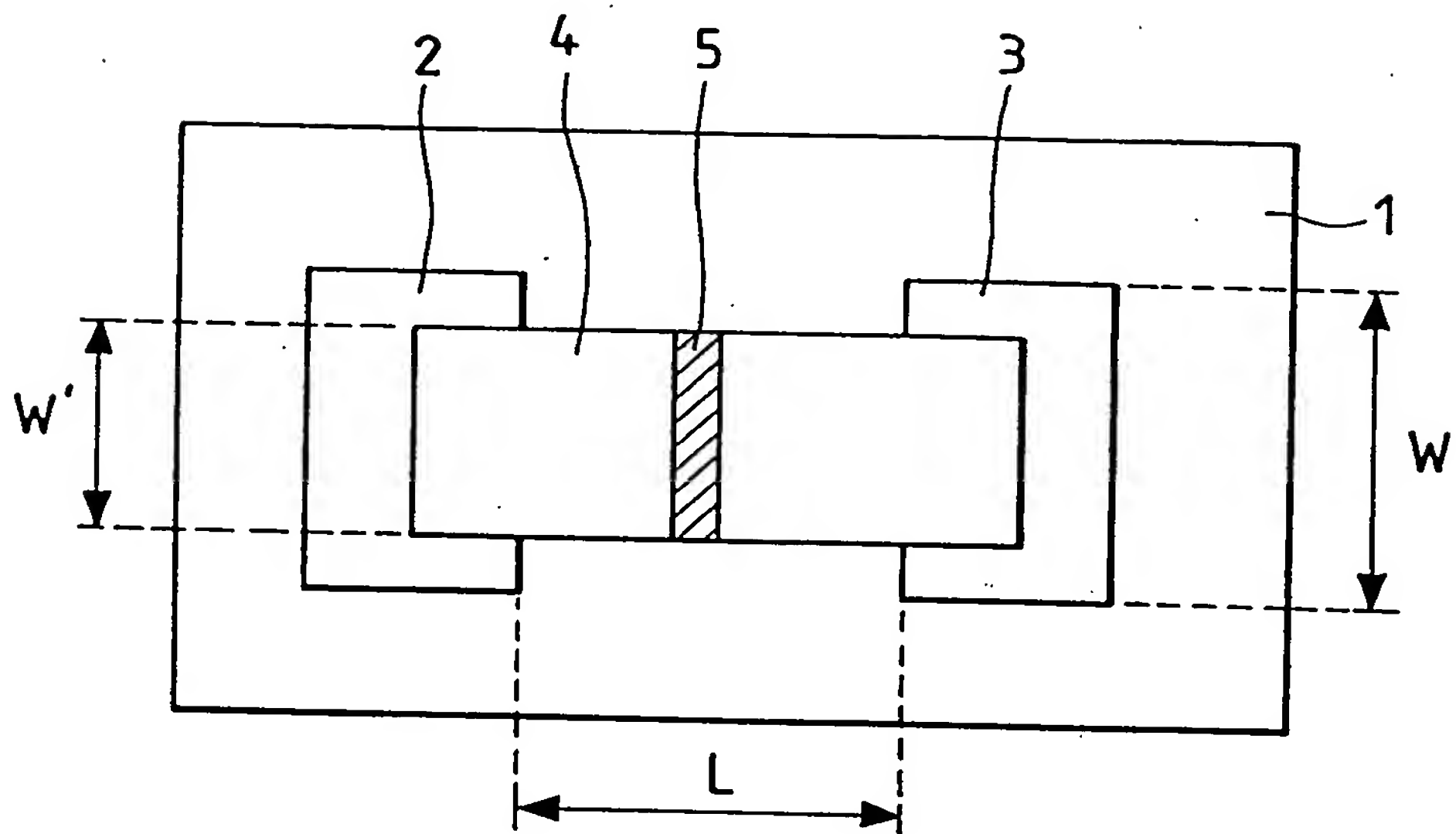


FIG. 9B

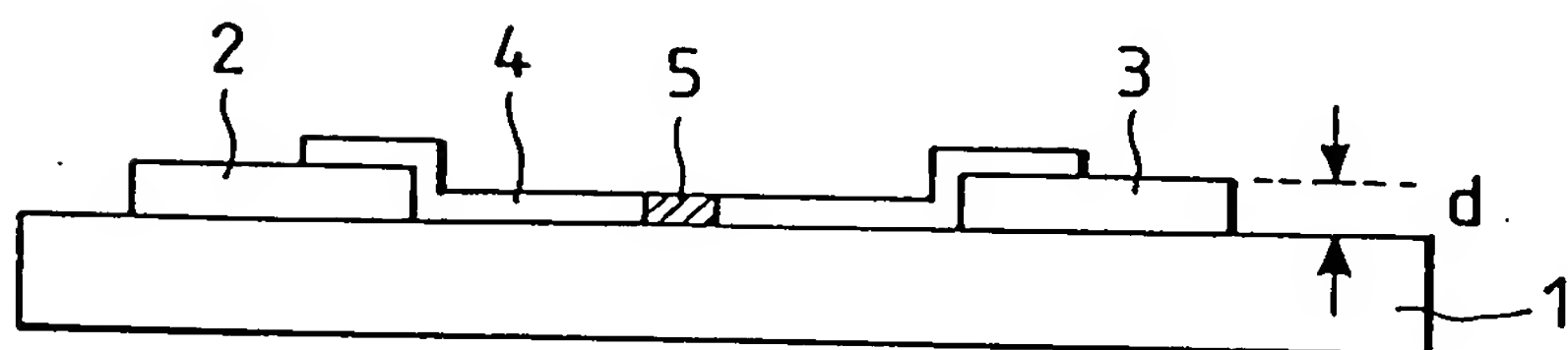


FIG. 10A

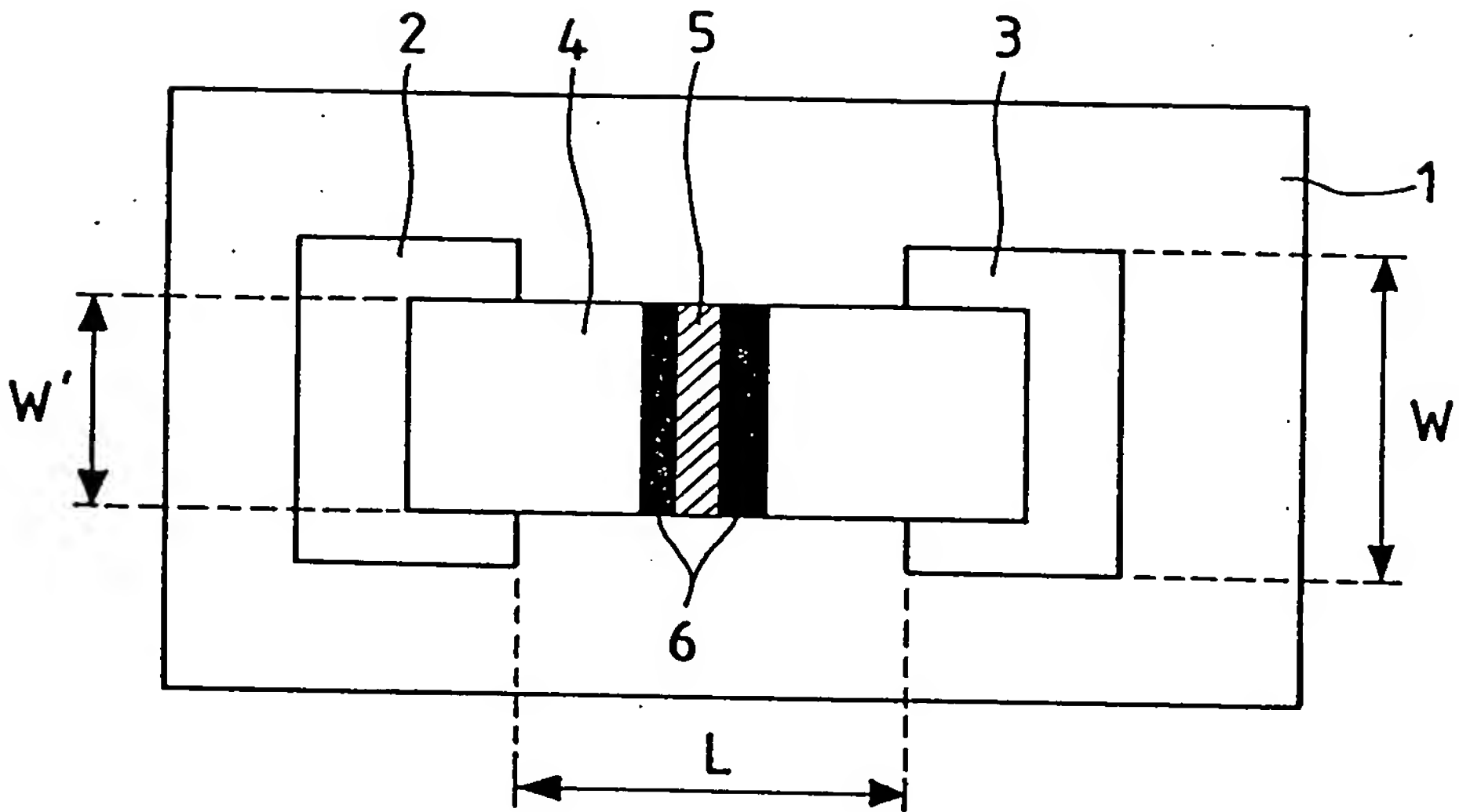
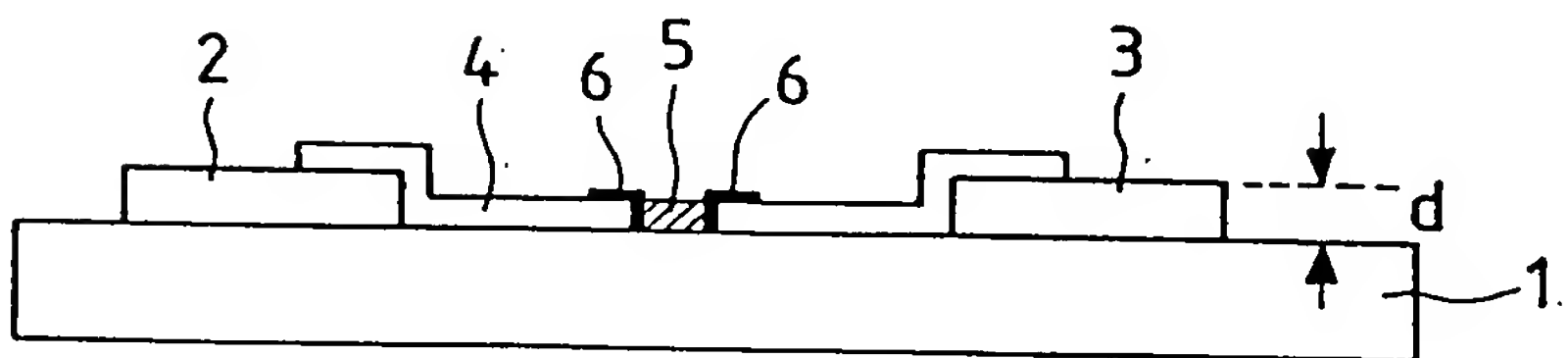


FIG. 10B



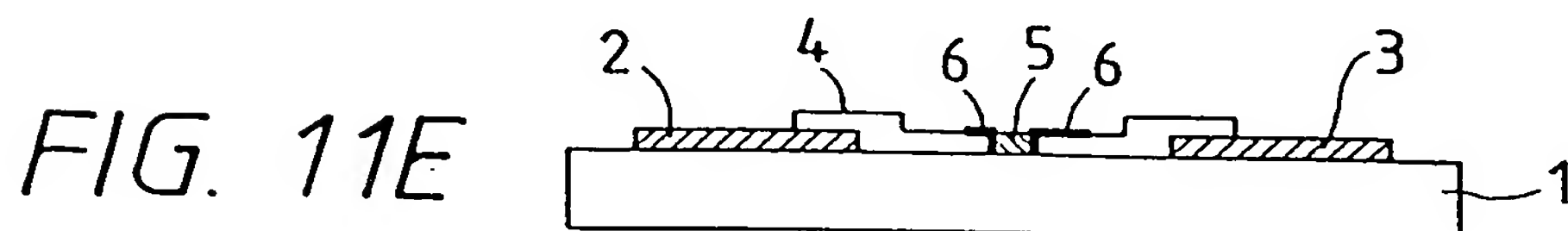
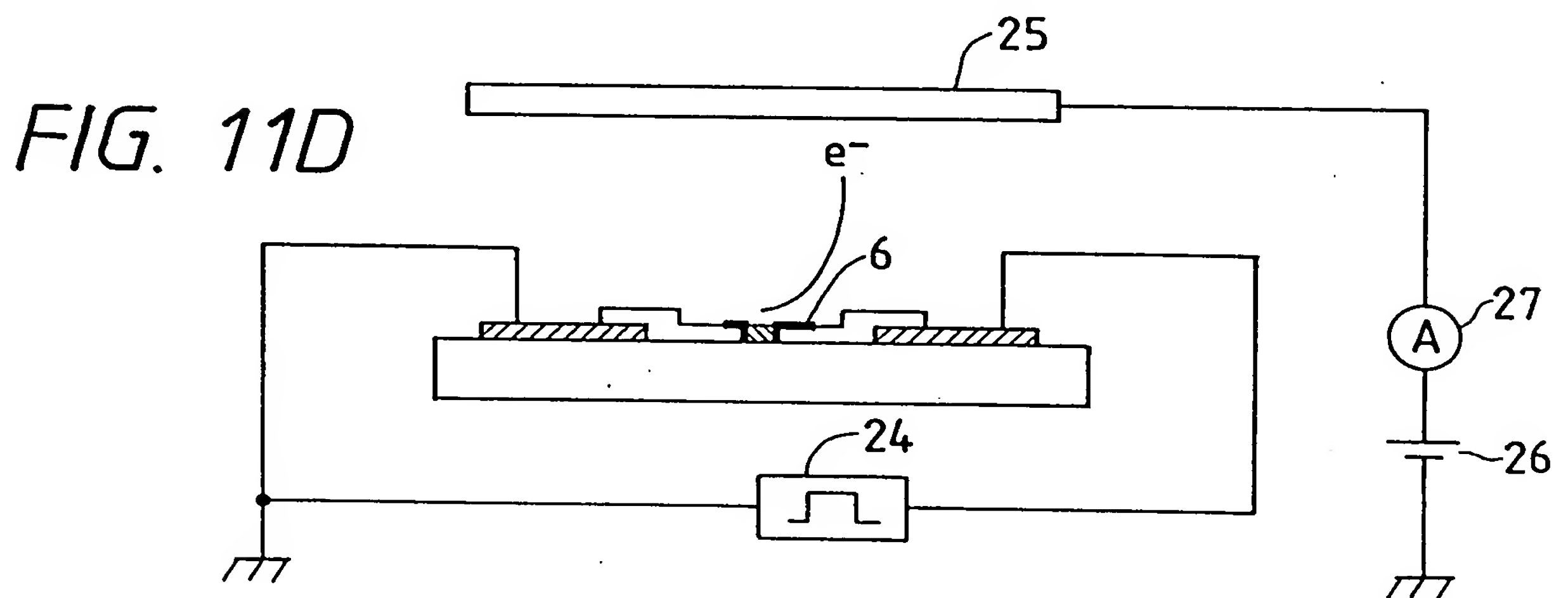
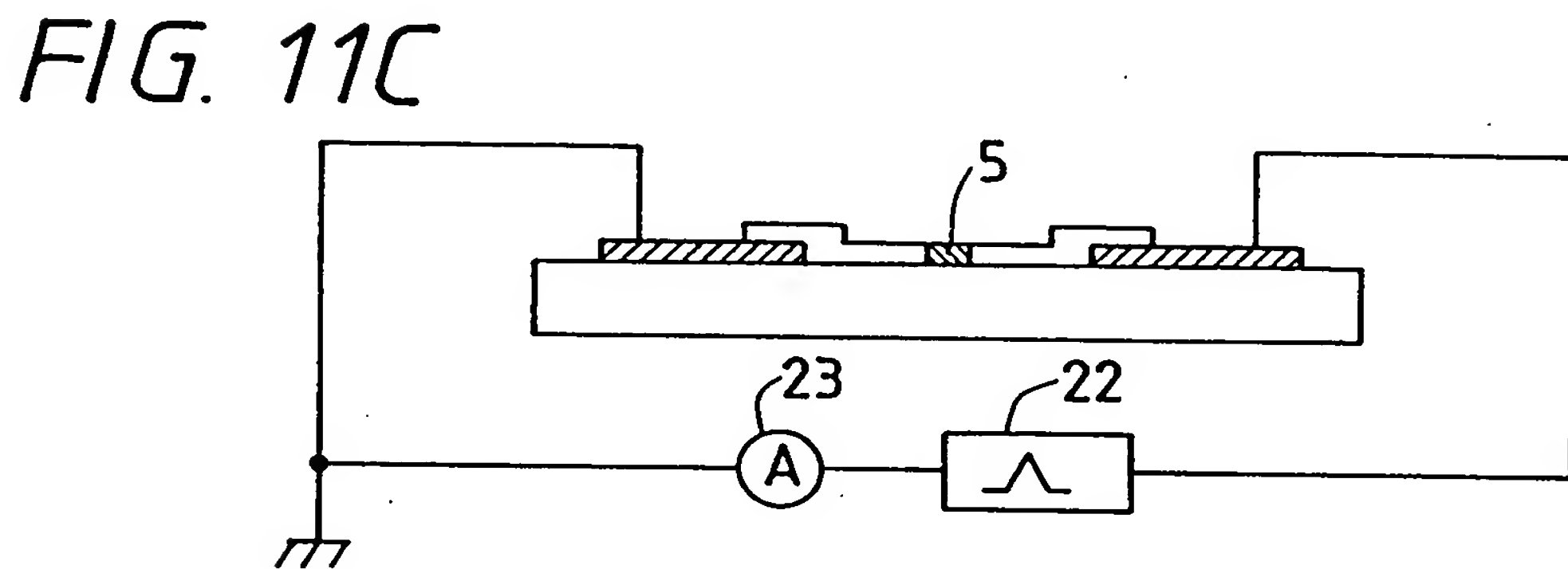
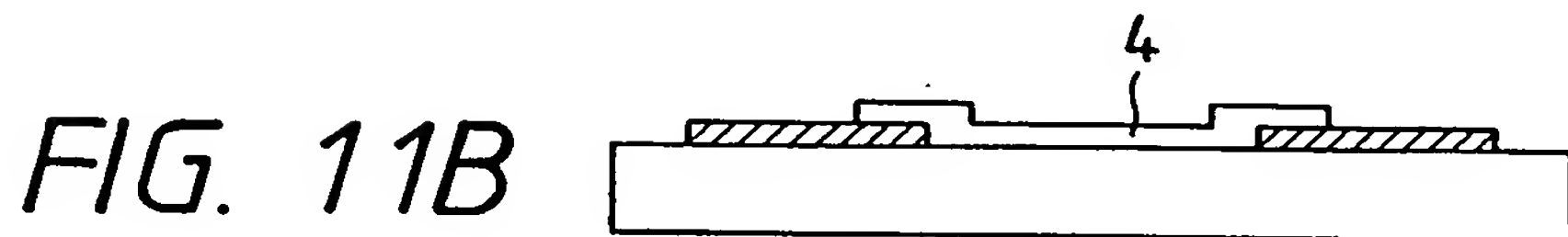
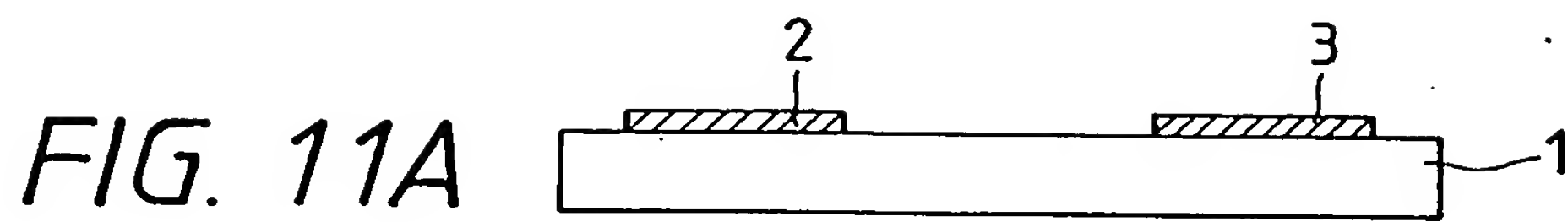


FIG. 12

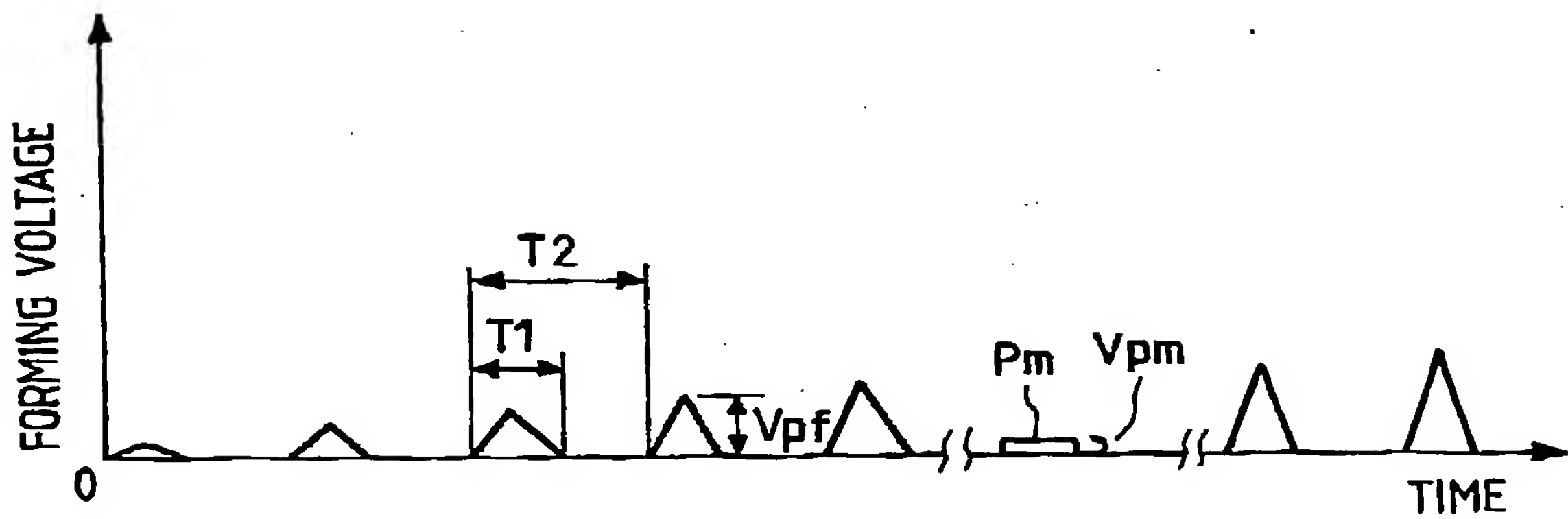


FIG. 13A

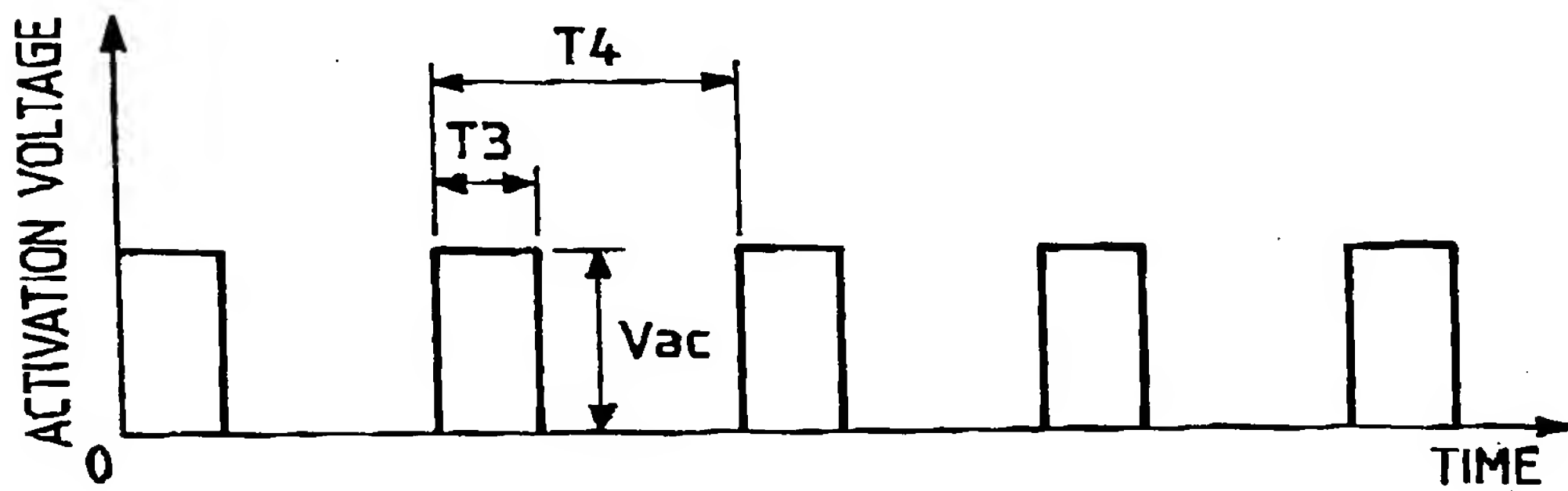


FIG. 13B

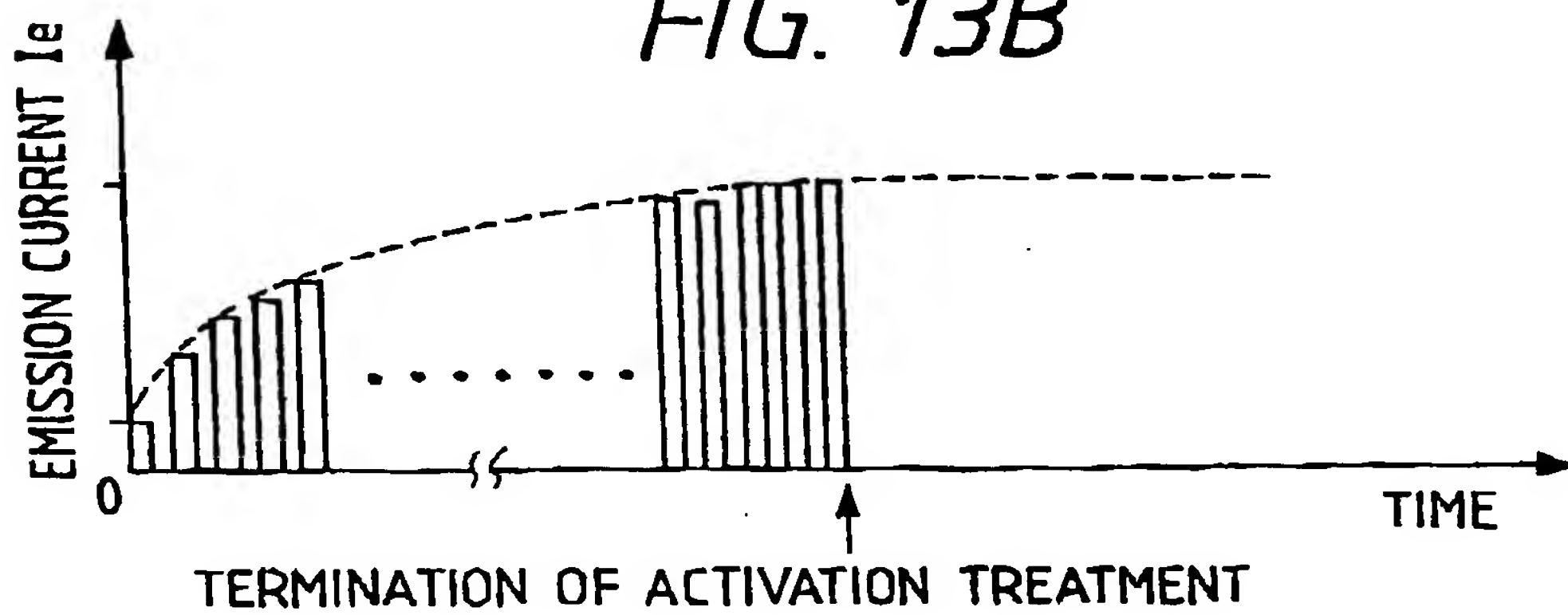


FIG. 14

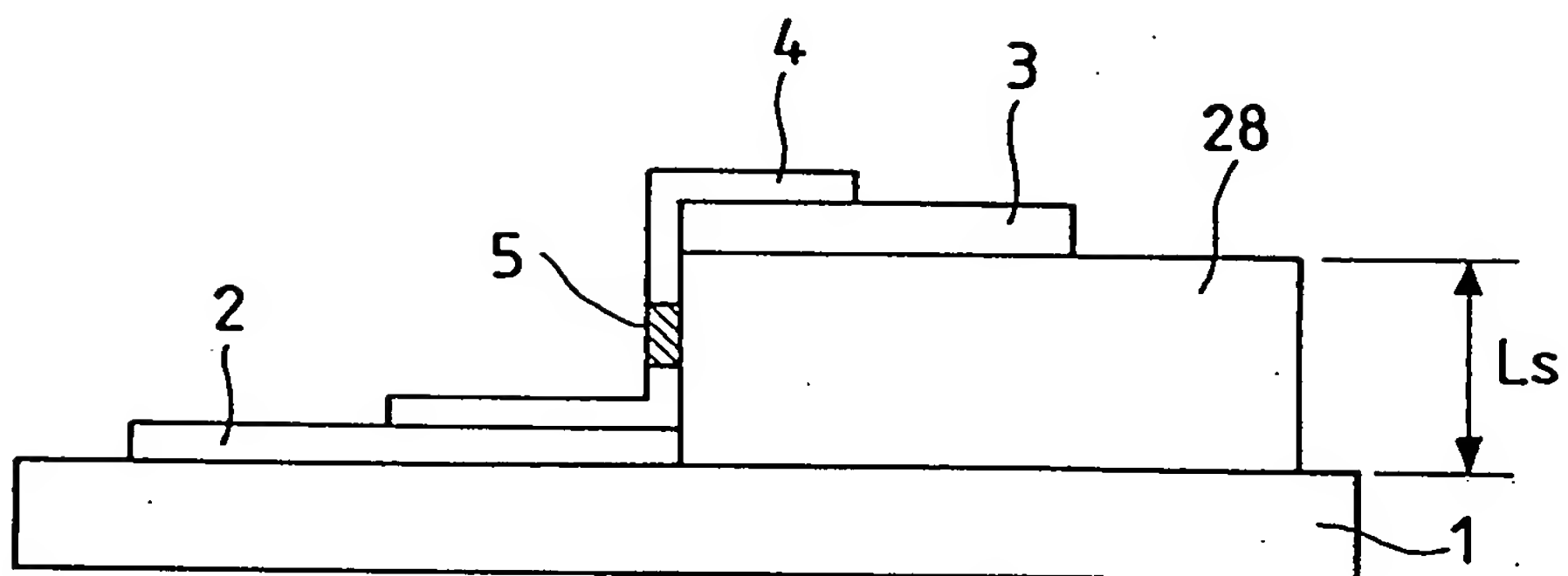


FIG. 15

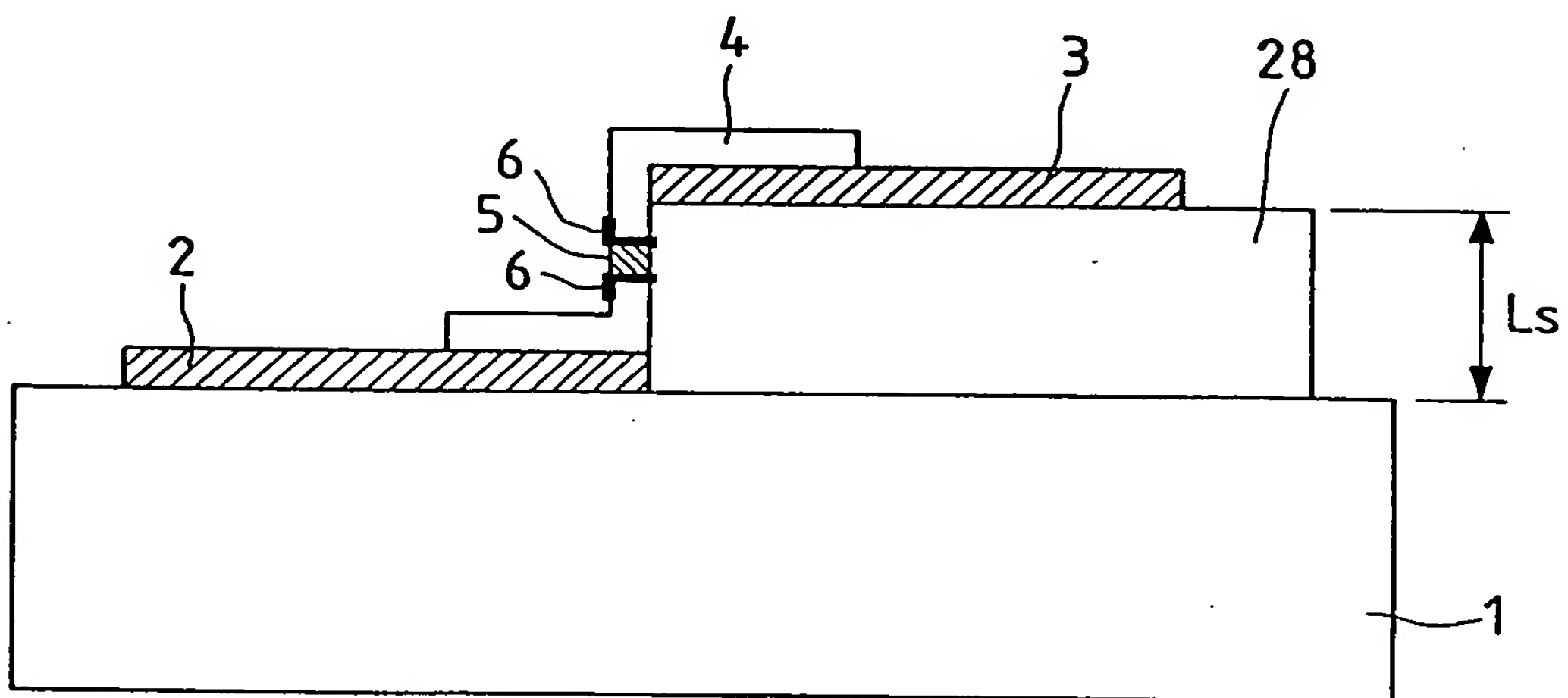


FIG. 16A

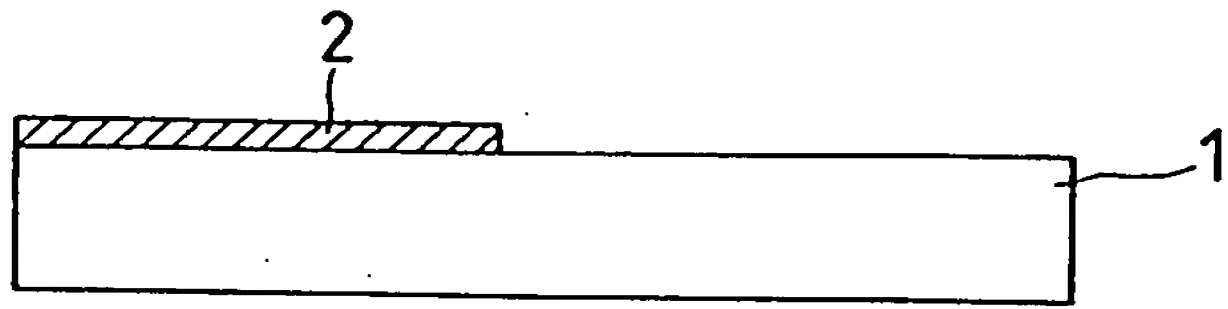


FIG. 16B

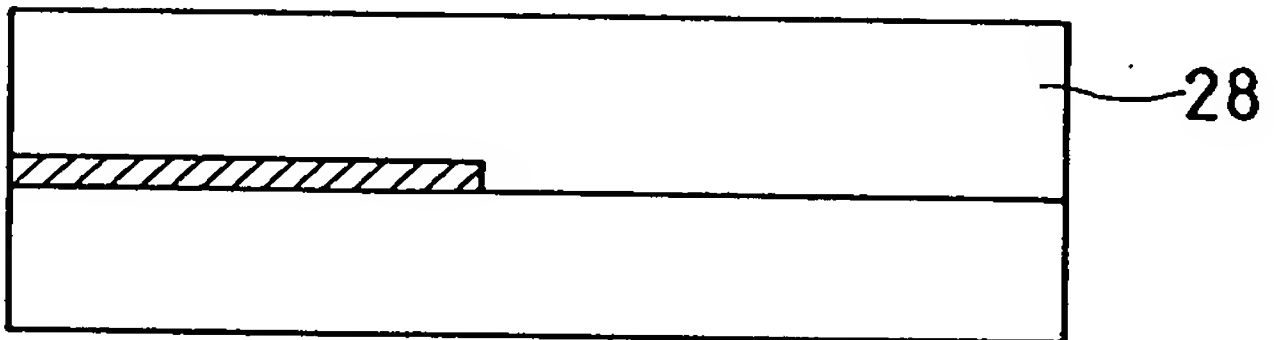


FIG. 16C

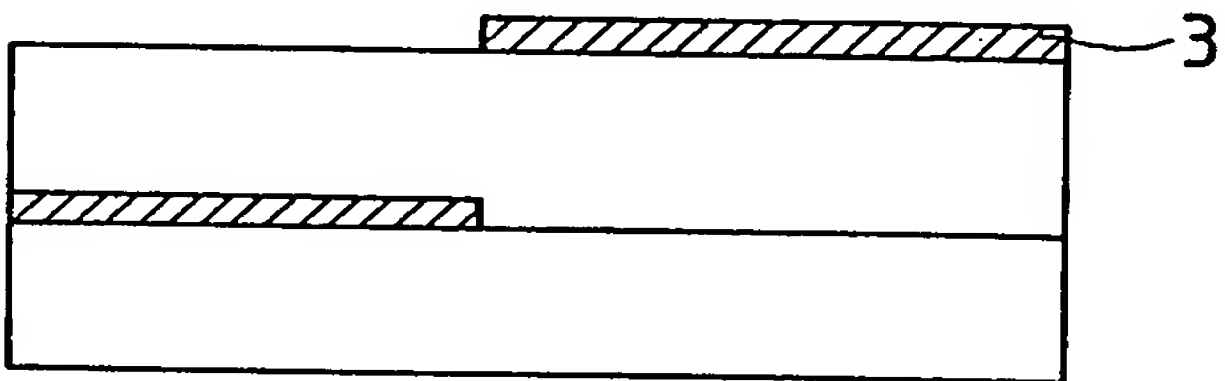


FIG. 16D

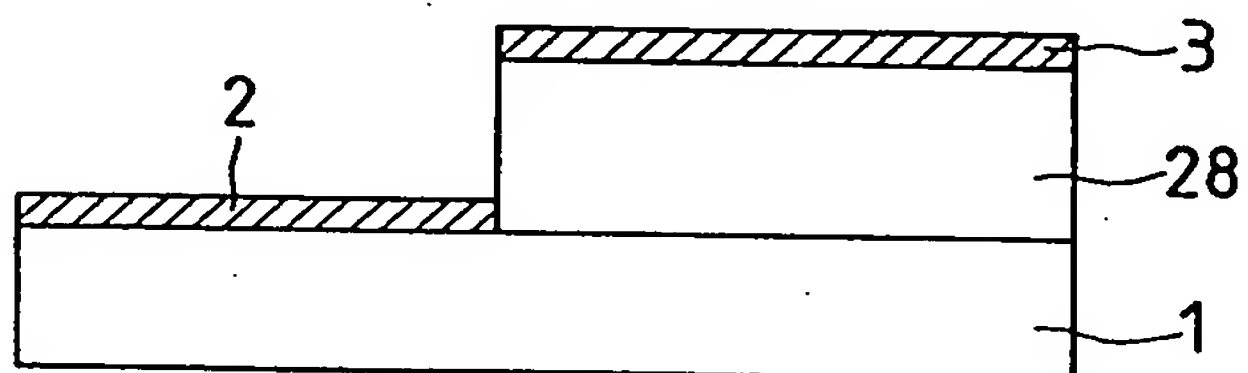


FIG. 16E

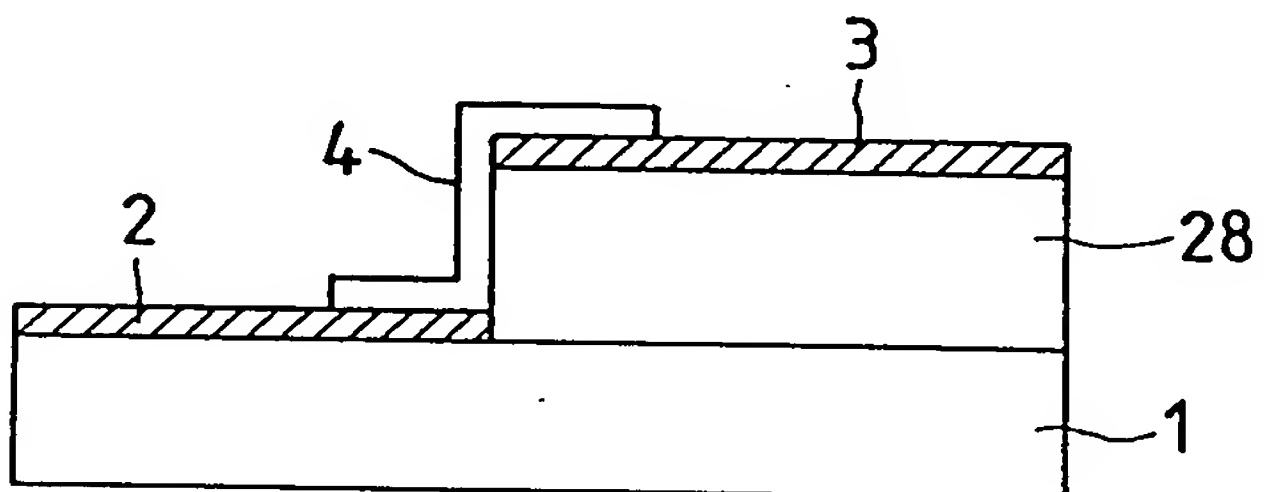


FIG. 16F

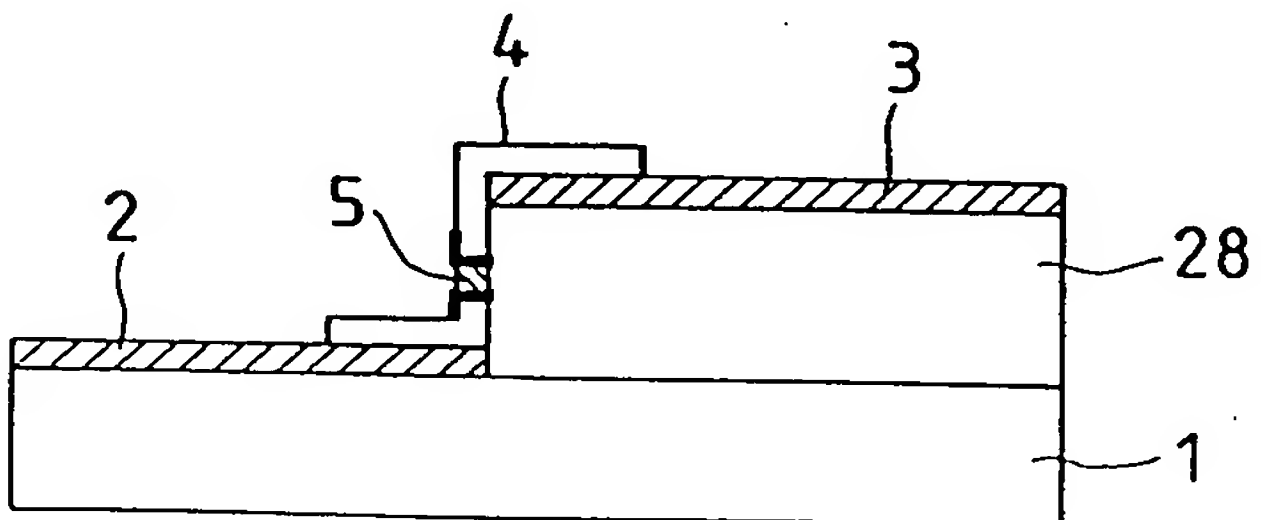


FIG. 17

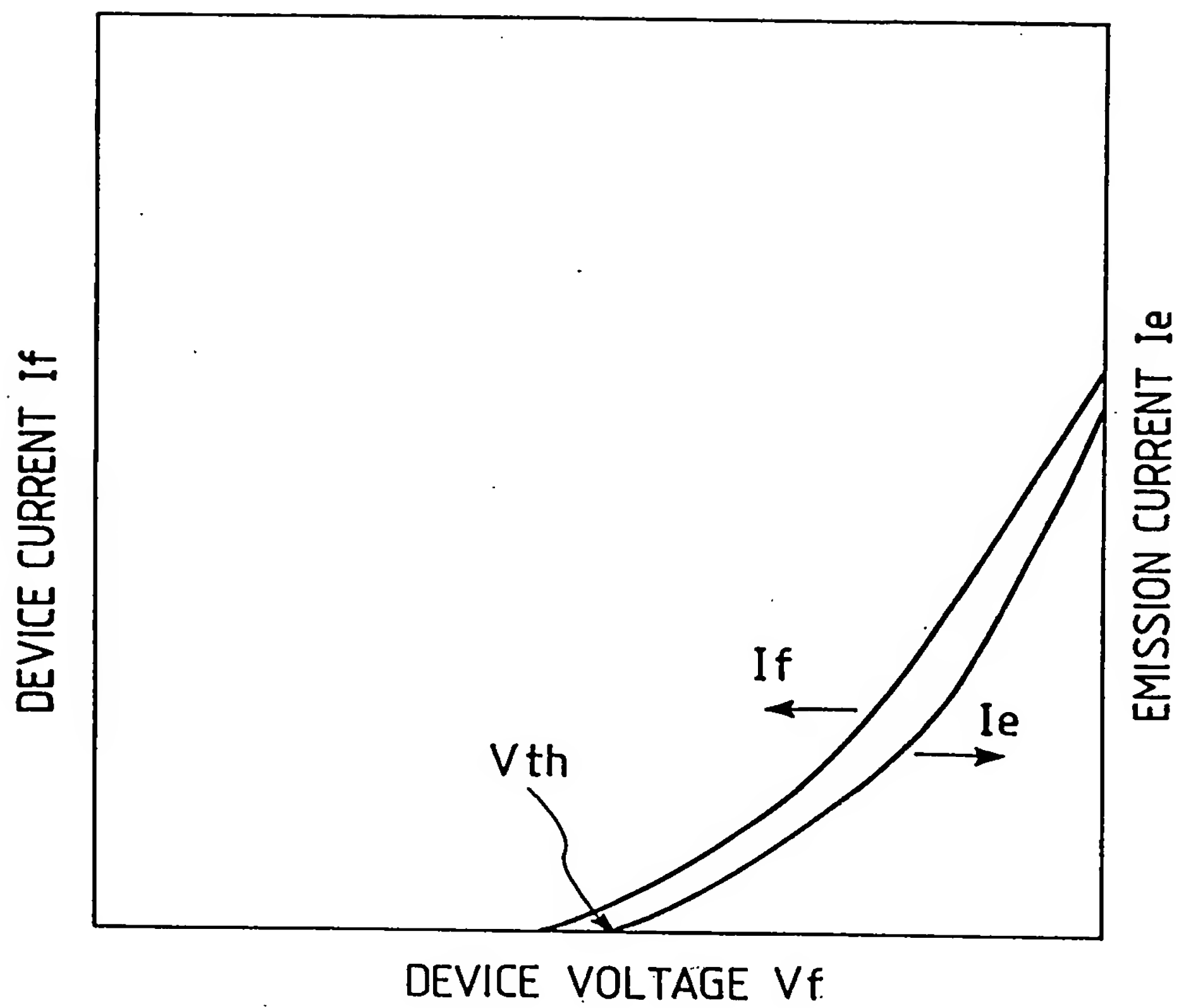


FIG. 18

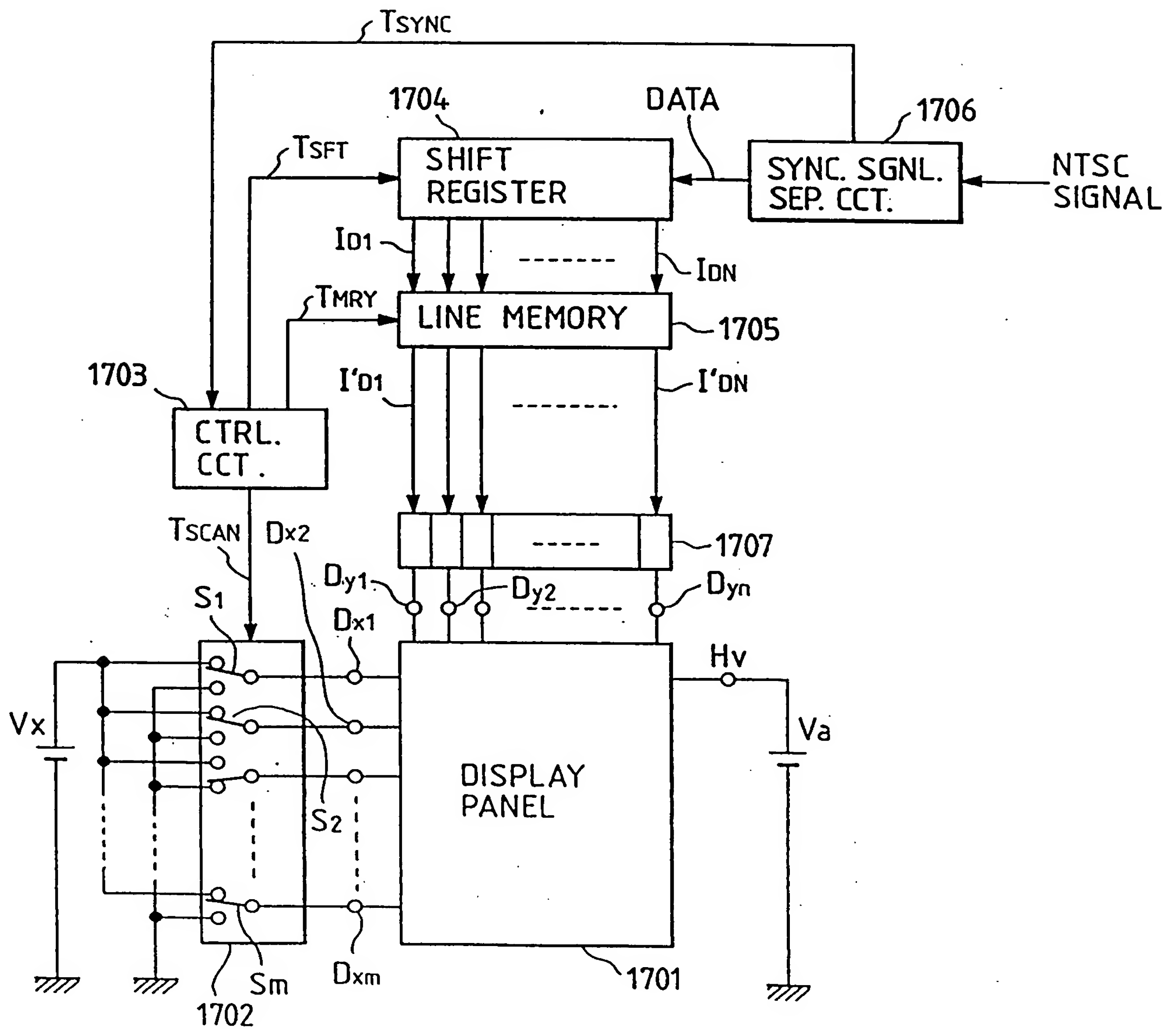
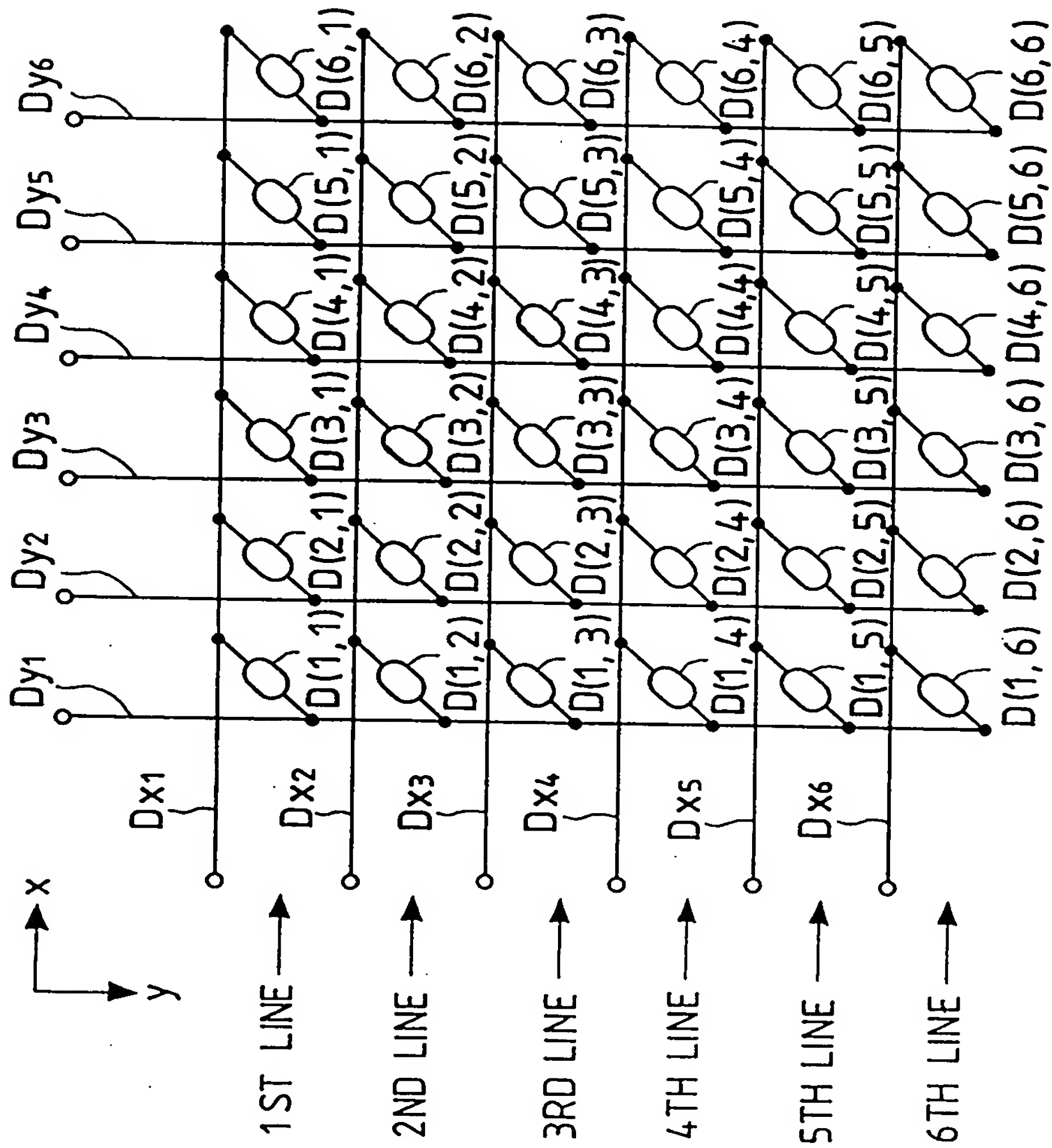
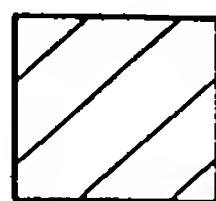
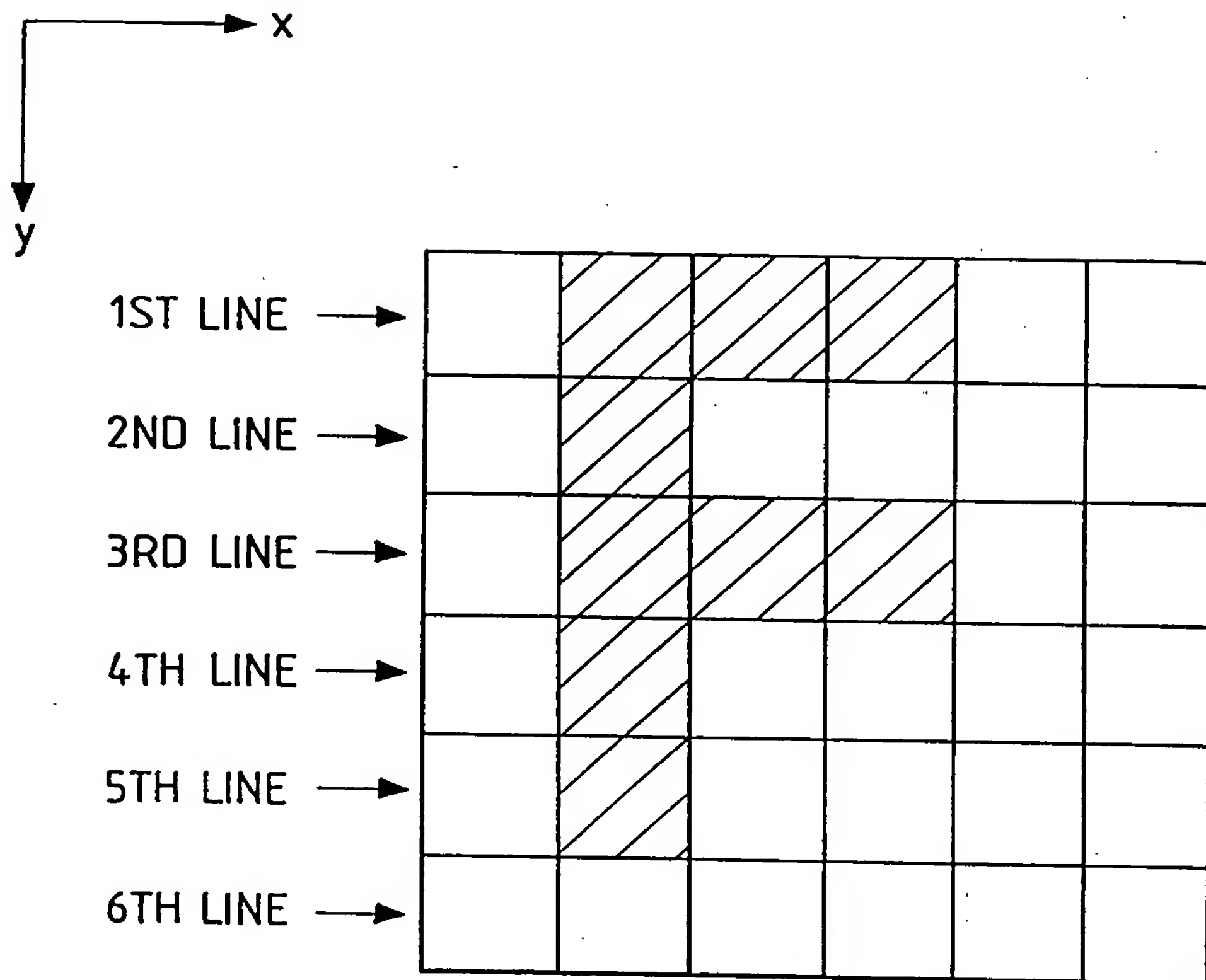


FIG. 19

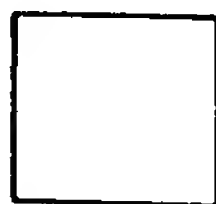


 : SURFACE CONDUCTION ELECTRON-EMITTING DEVICE

FIG. 20

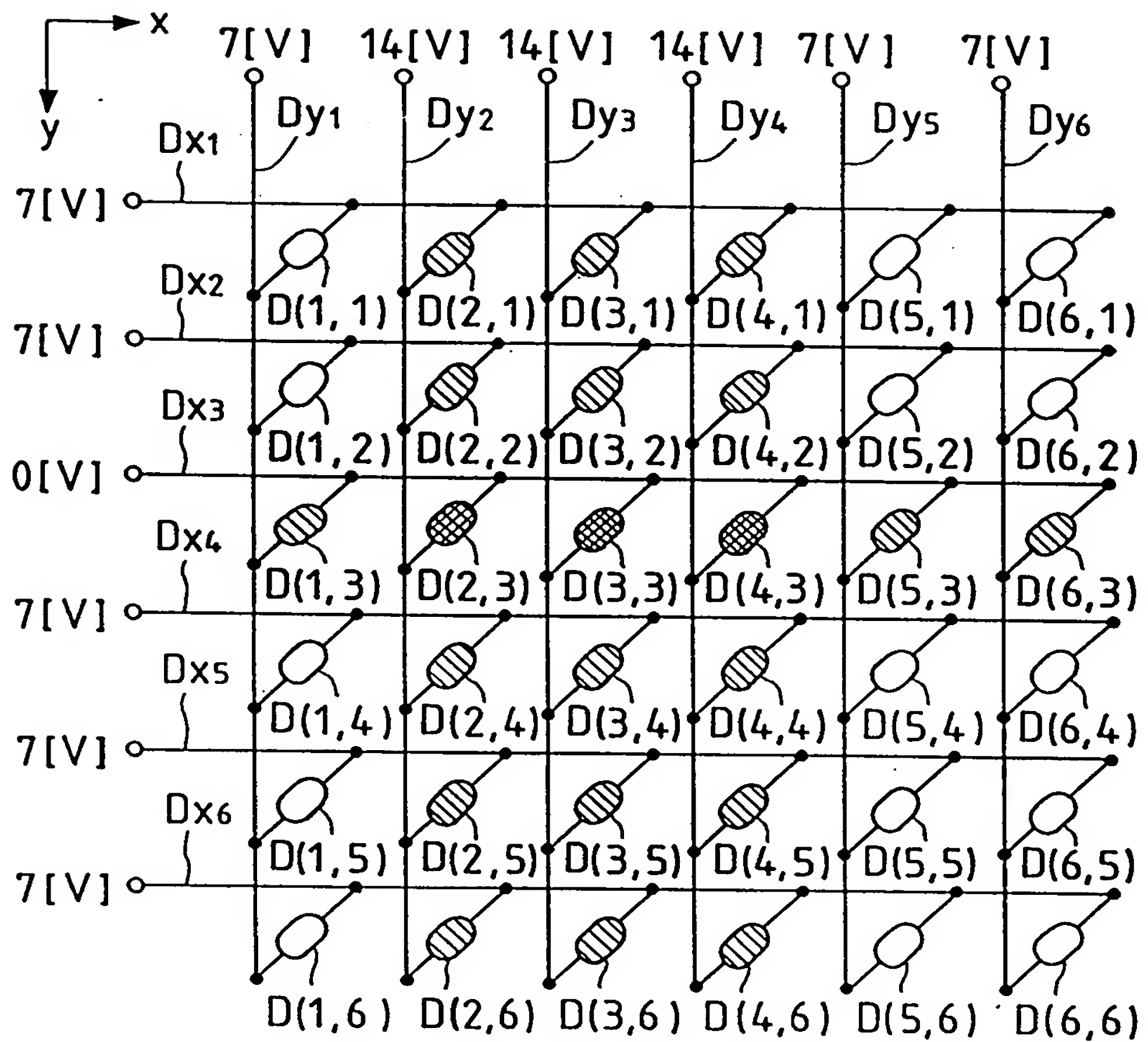


: LUMINOUS



: NON-LUMINOUS

FIG. 21






-  : 14V APPLIED
-  : 7V APPLIED
-  : 0V APPLIED

FIG. 22A

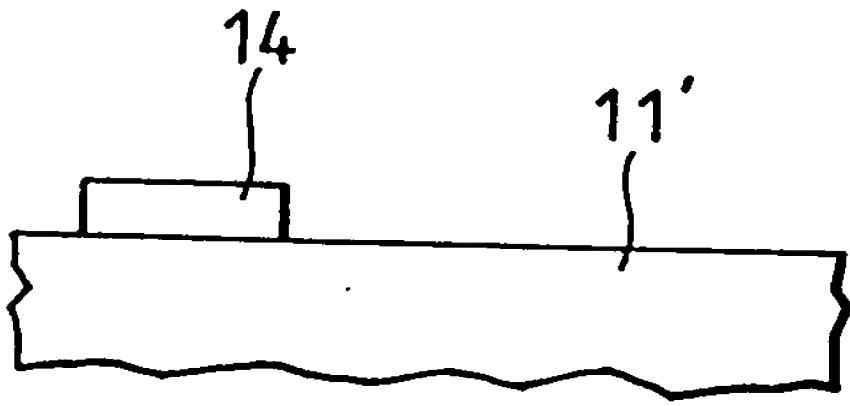


FIG. 22E

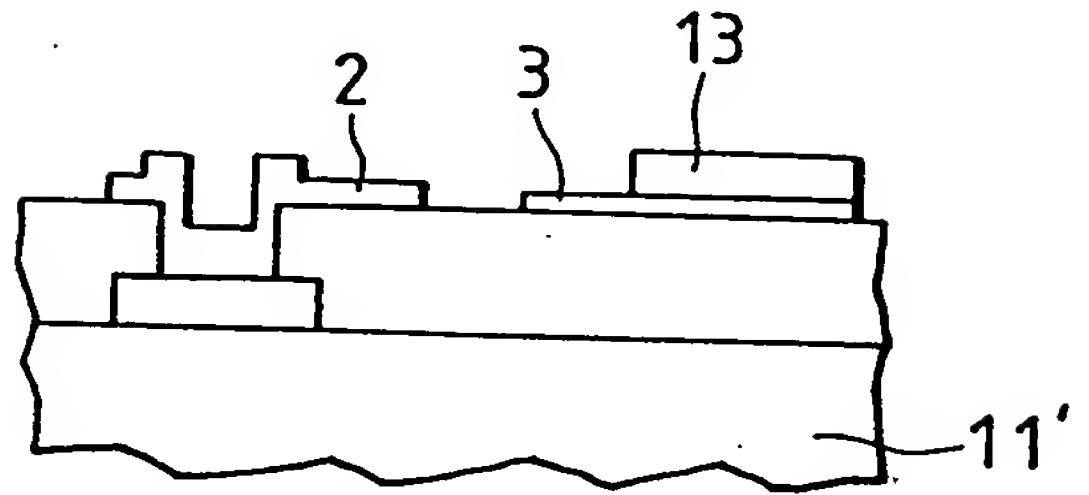


FIG. 22B

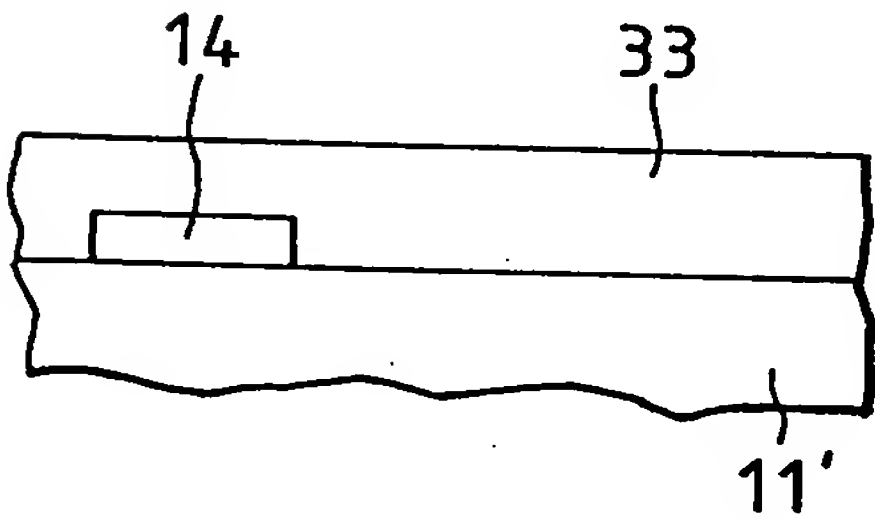


FIG. 22F

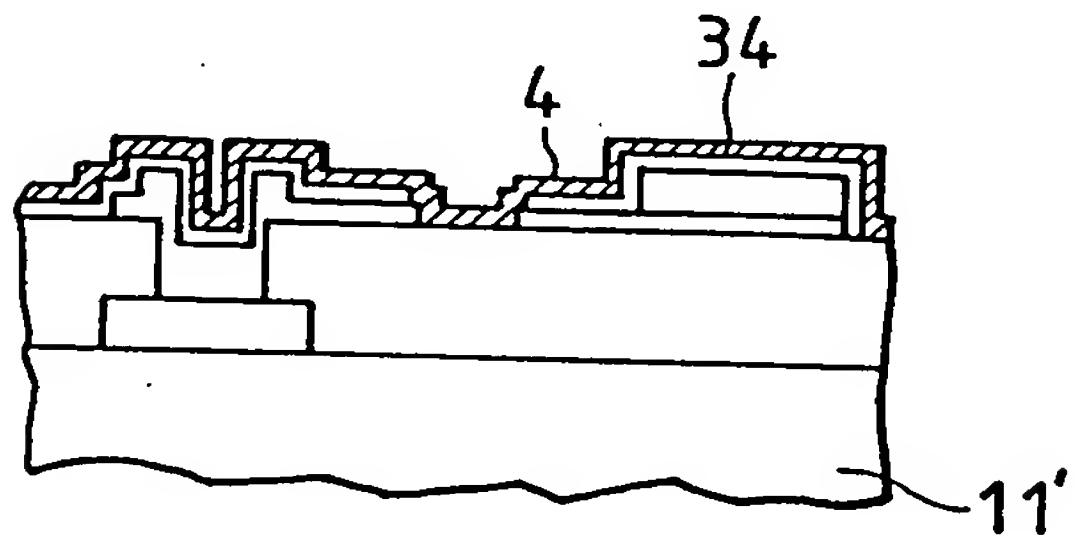


FIG. 22C

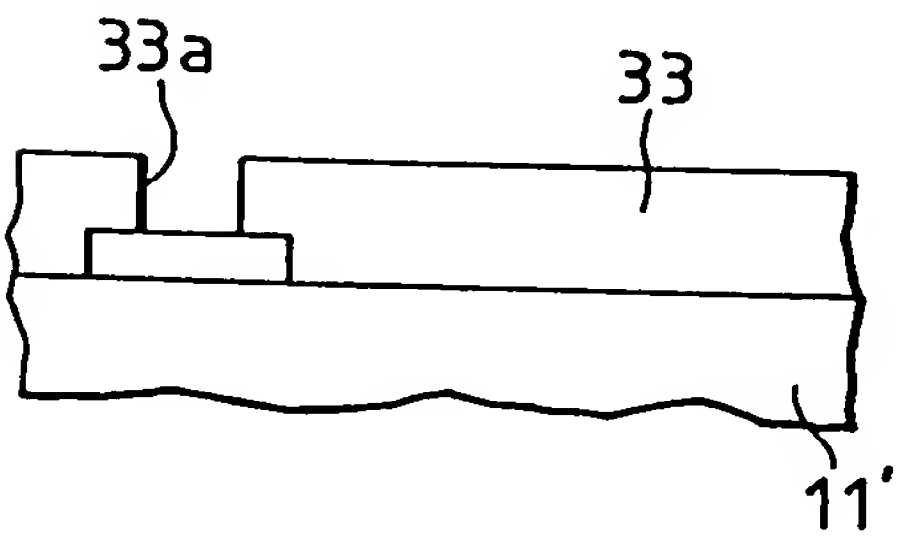


FIG. 22G

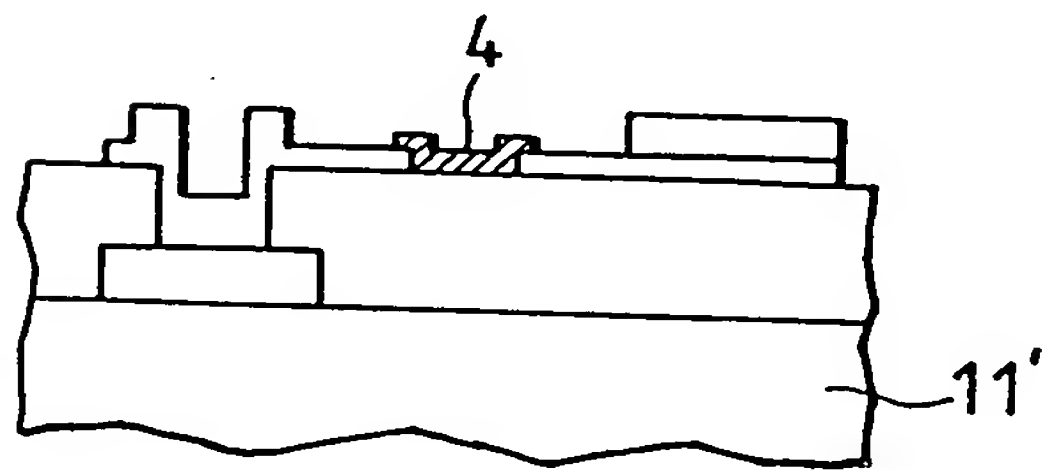


FIG. 22D

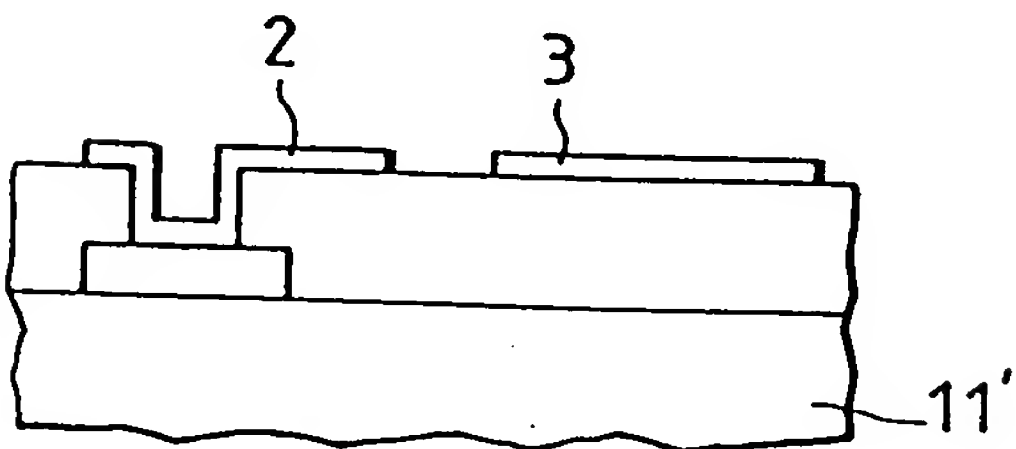
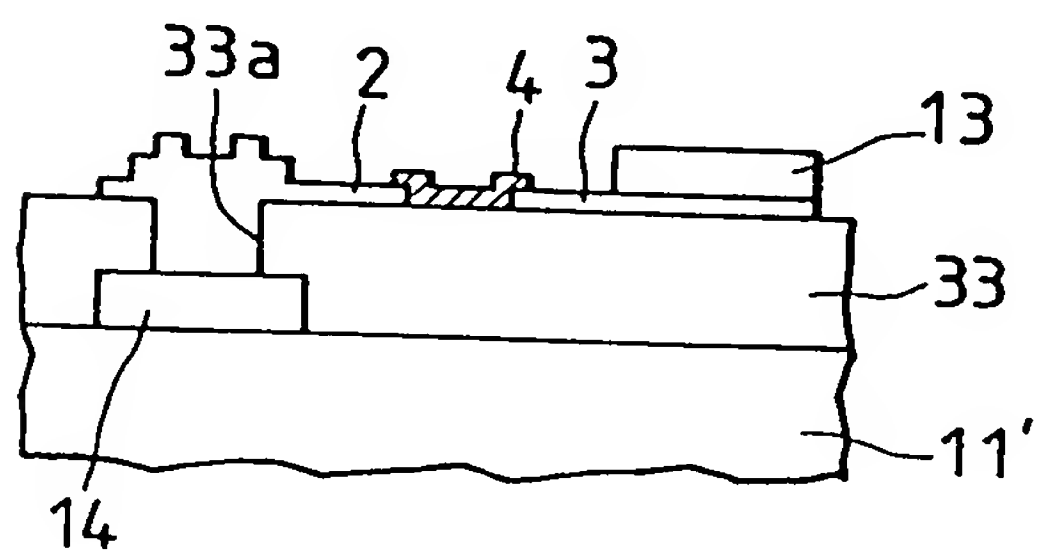


FIG. 22H



09045681.032398
85E28D T8954050

FIG. 23.

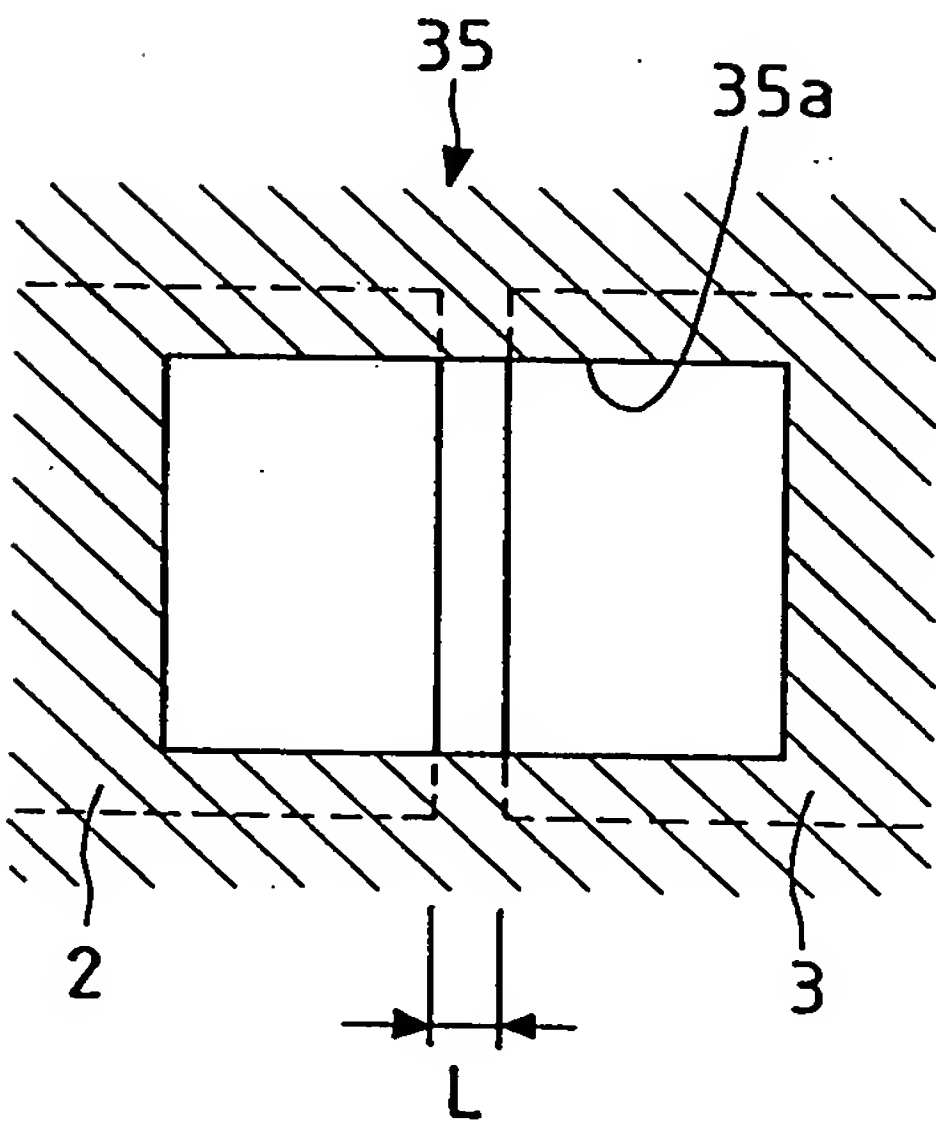


FIG. 24

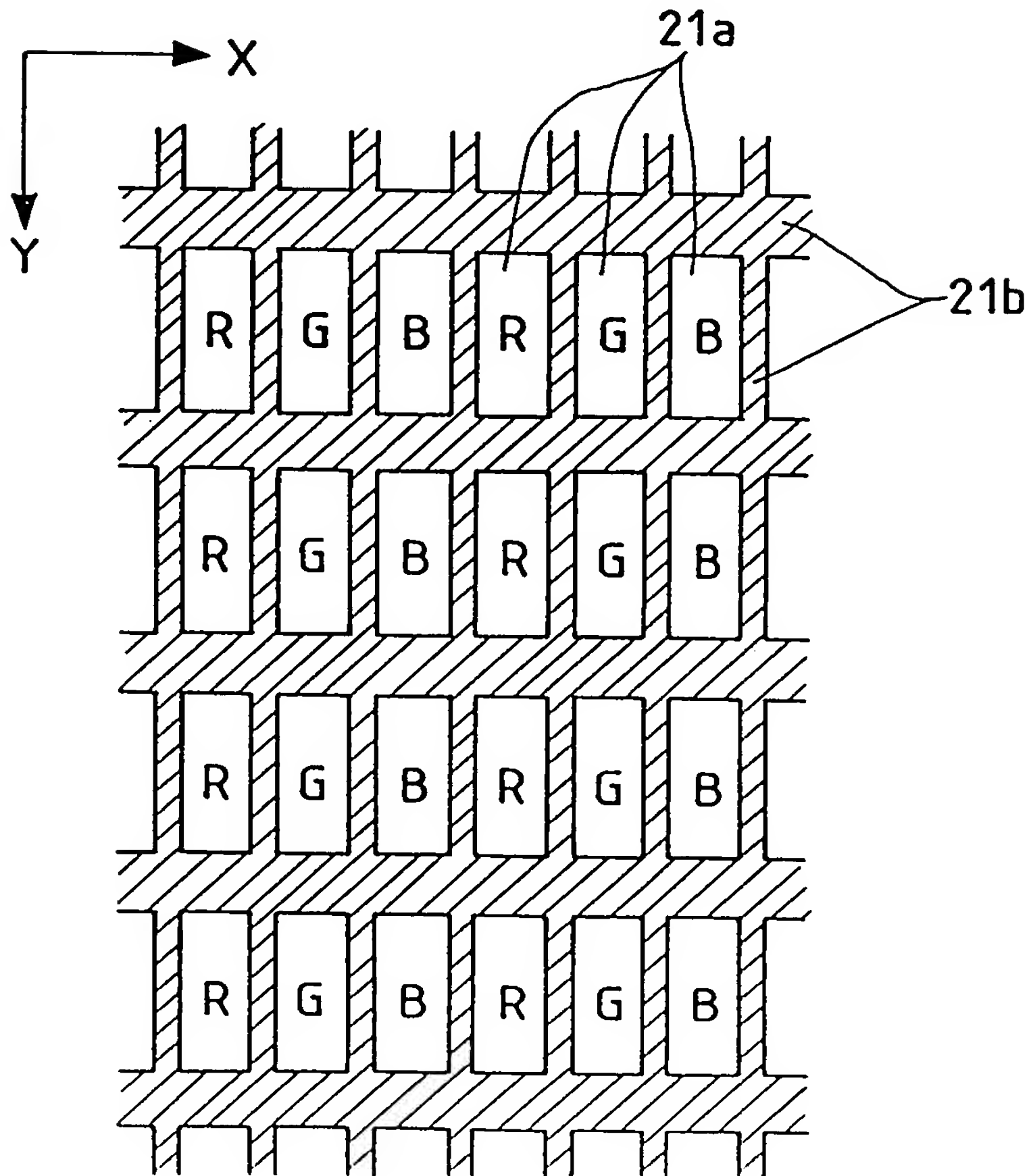


FIG. 25

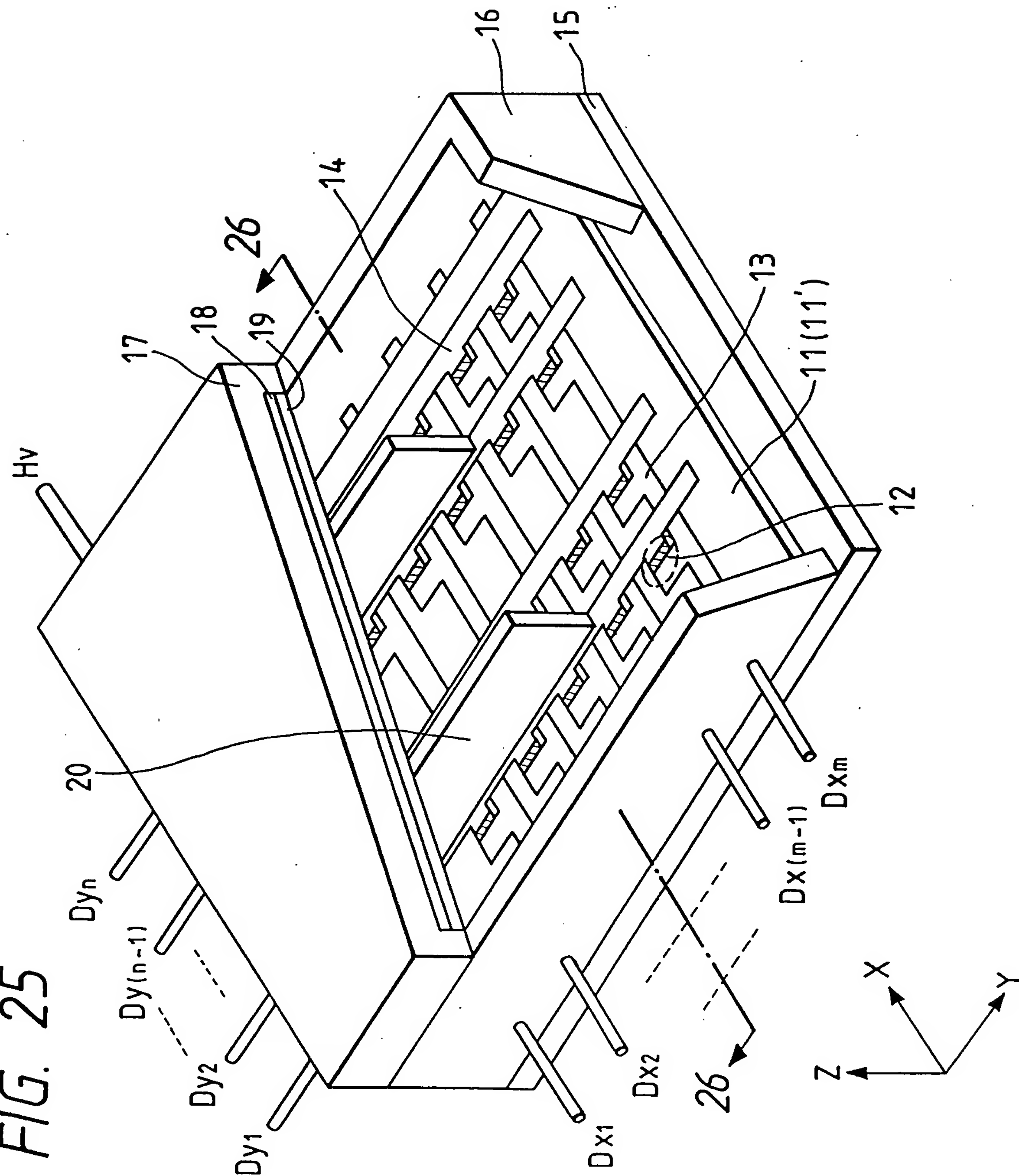


FIG. 26

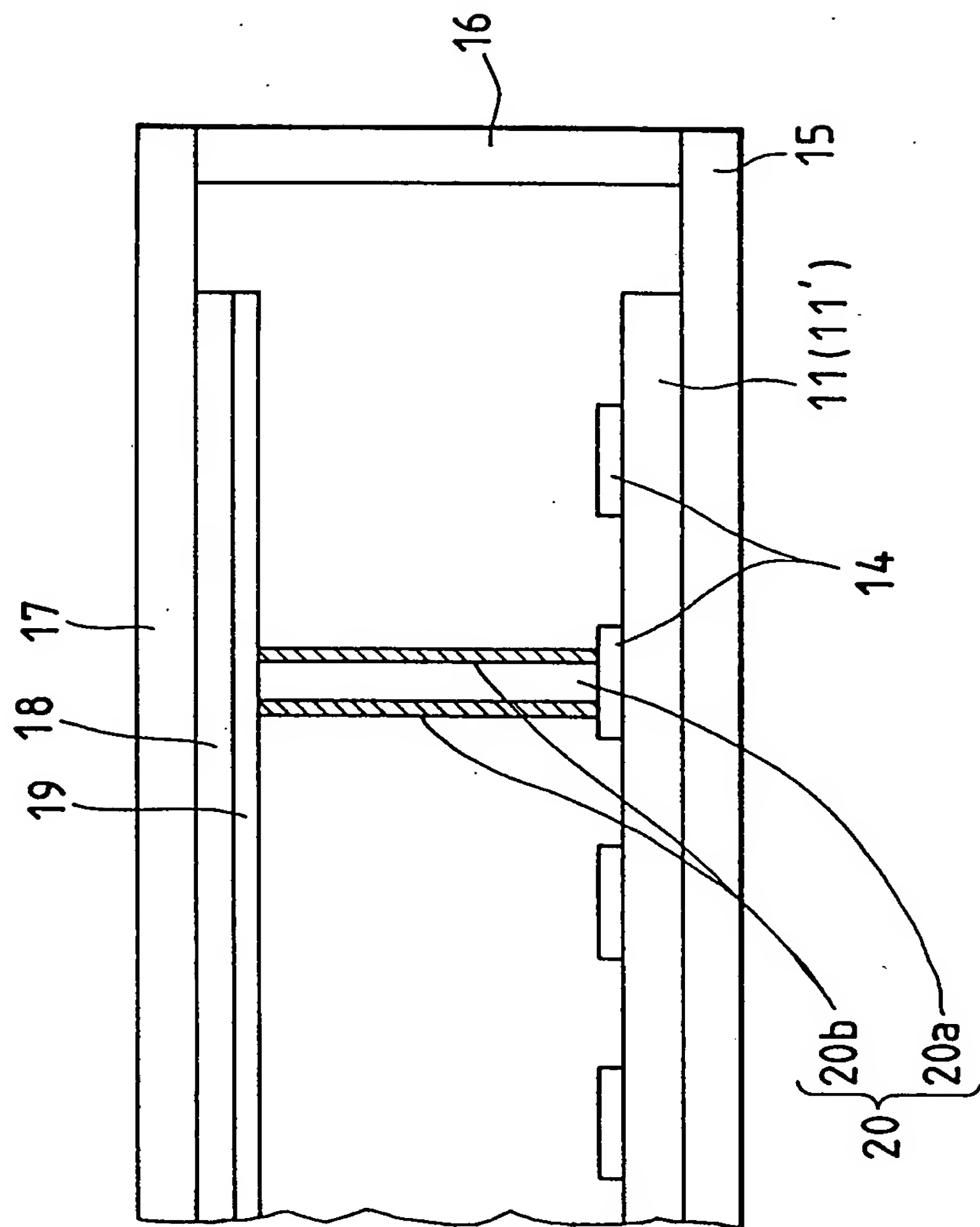
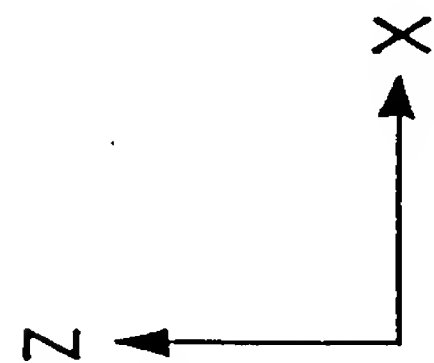


FIG. 30

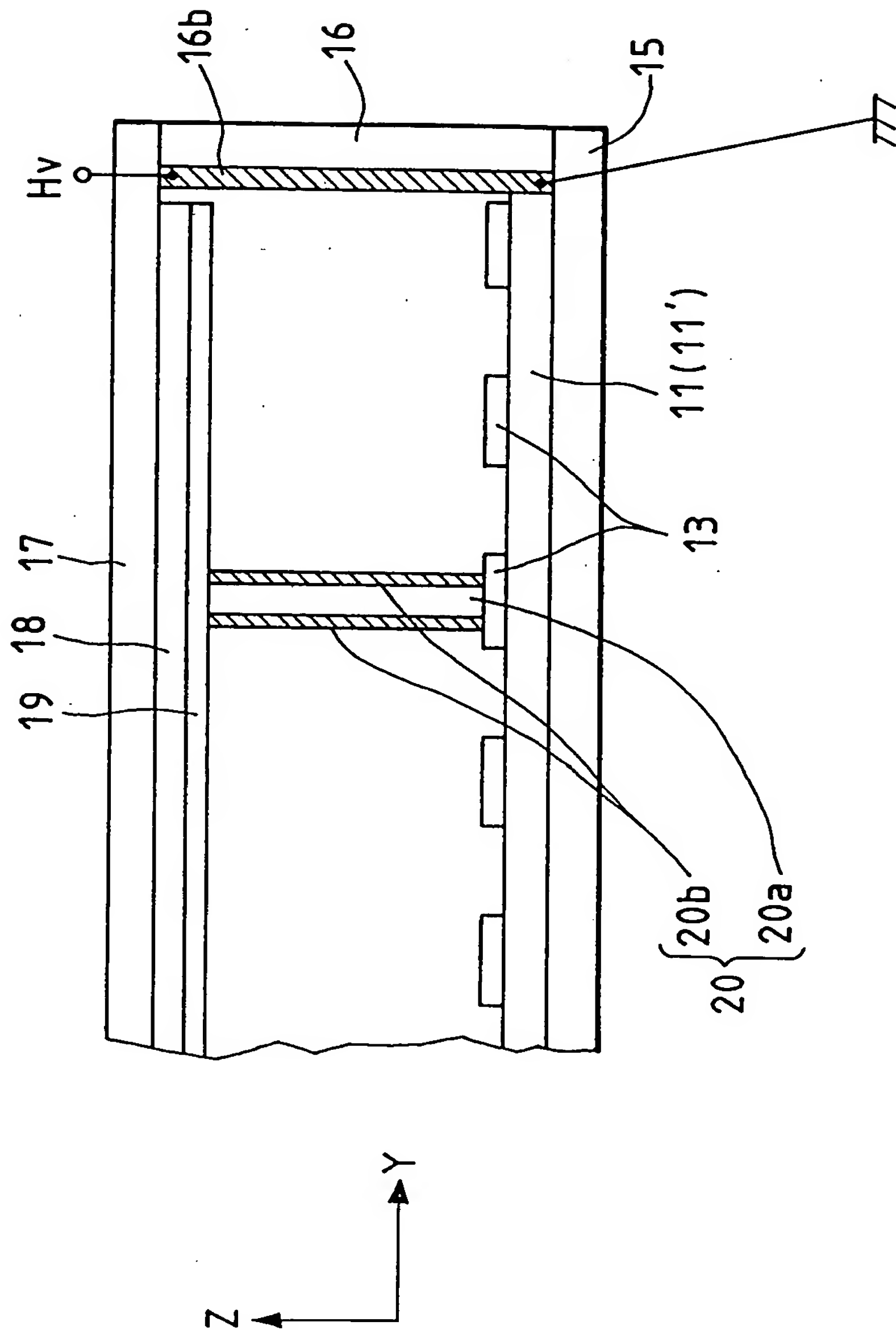


FIG. 34A

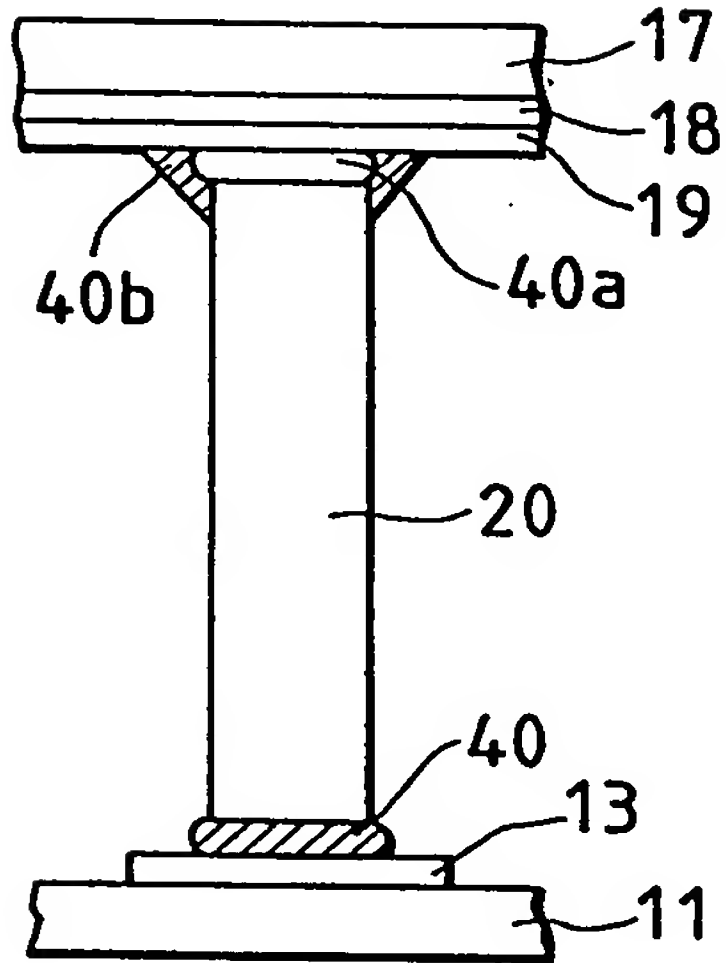


FIG. 34B

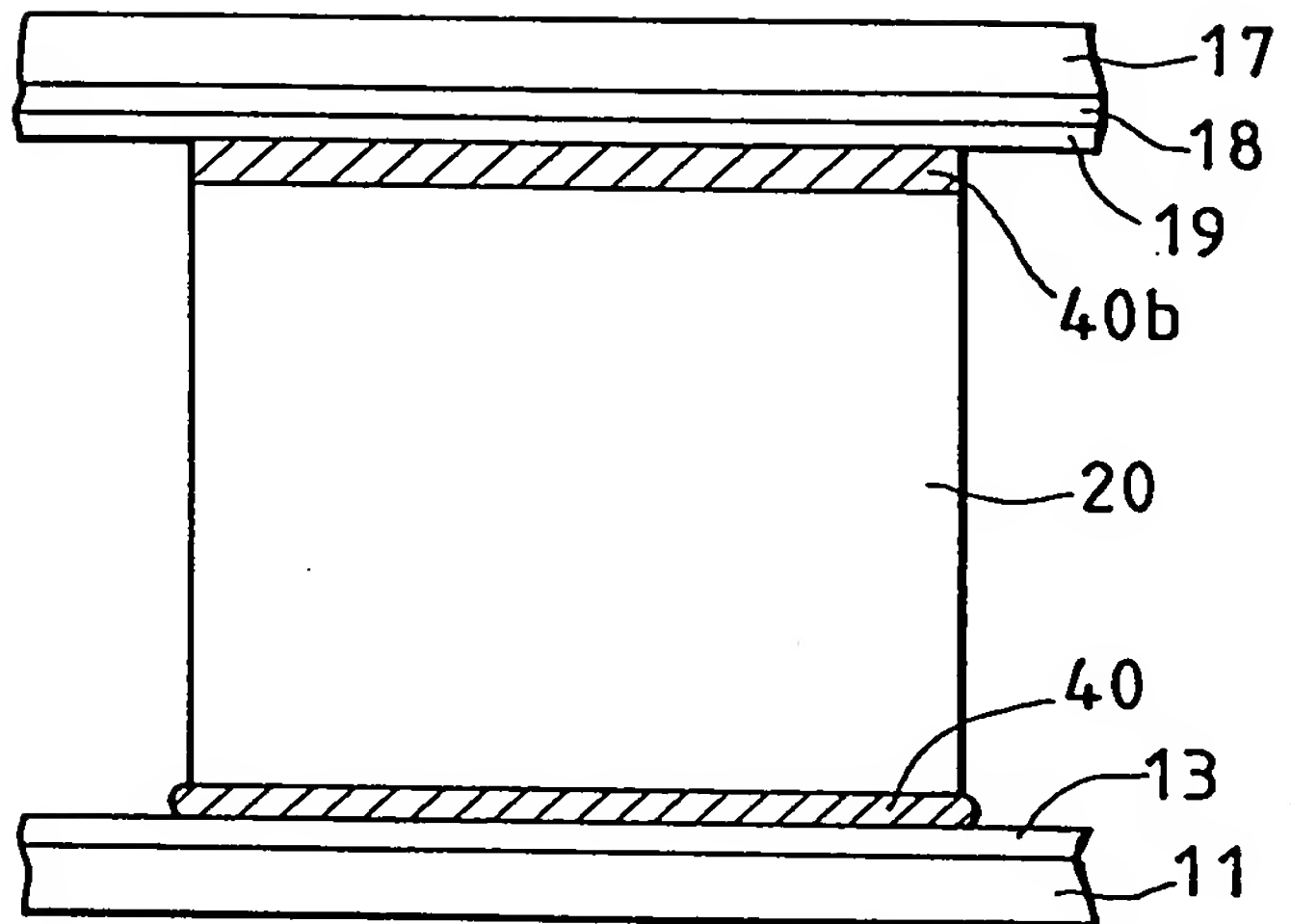


FIG. 36 PRIOR ART

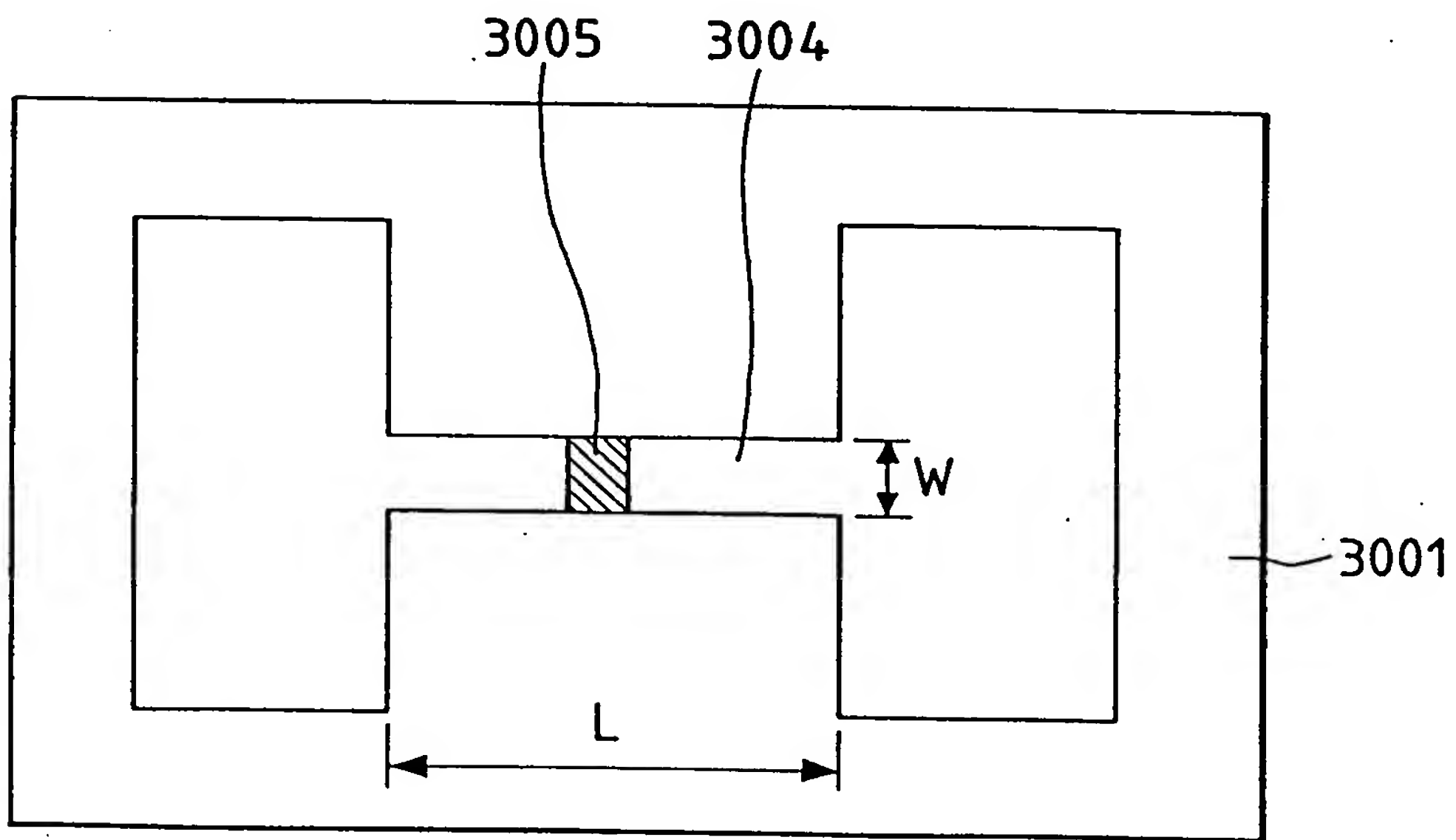
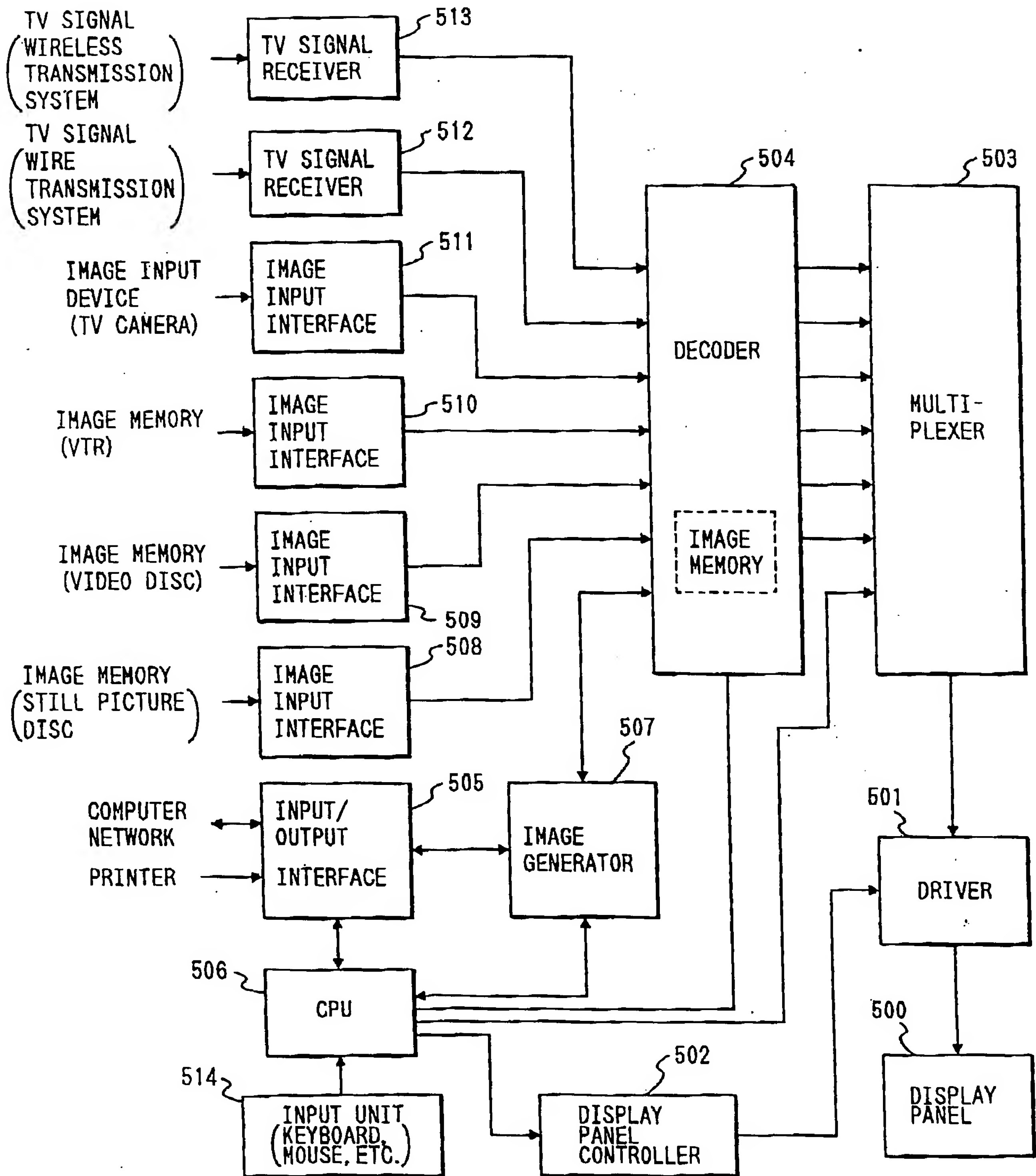


FIG. 35



00045681-032298

A cross-sectional view of a semiconductor device. The device consists of a substrate 3010, a thin layer 3011, and a layer 3013. A central peak 3012 is formed on the surface of layer 3013. Two rectangular regions 3014 are located on the surface of layer 3013, one on each side of the peak 3012. An arrow labeled e^- points upwards from the peak 3012, indicating electron emission.

A cross-sectional diagram of a device structure 3000. The structure consists of a substrate 3020 at the bottom, which is a large white rectangle. Above the substrate is a stack of three layers: a bottom layer 3021 with diagonal hatching, a middle layer 3022 with a stippled pattern, and a top layer 3023 with diagonal hatching. Above the top layer 3023, there is an upward-pointing arrow labeled e^- , indicating electron emission or current flow.